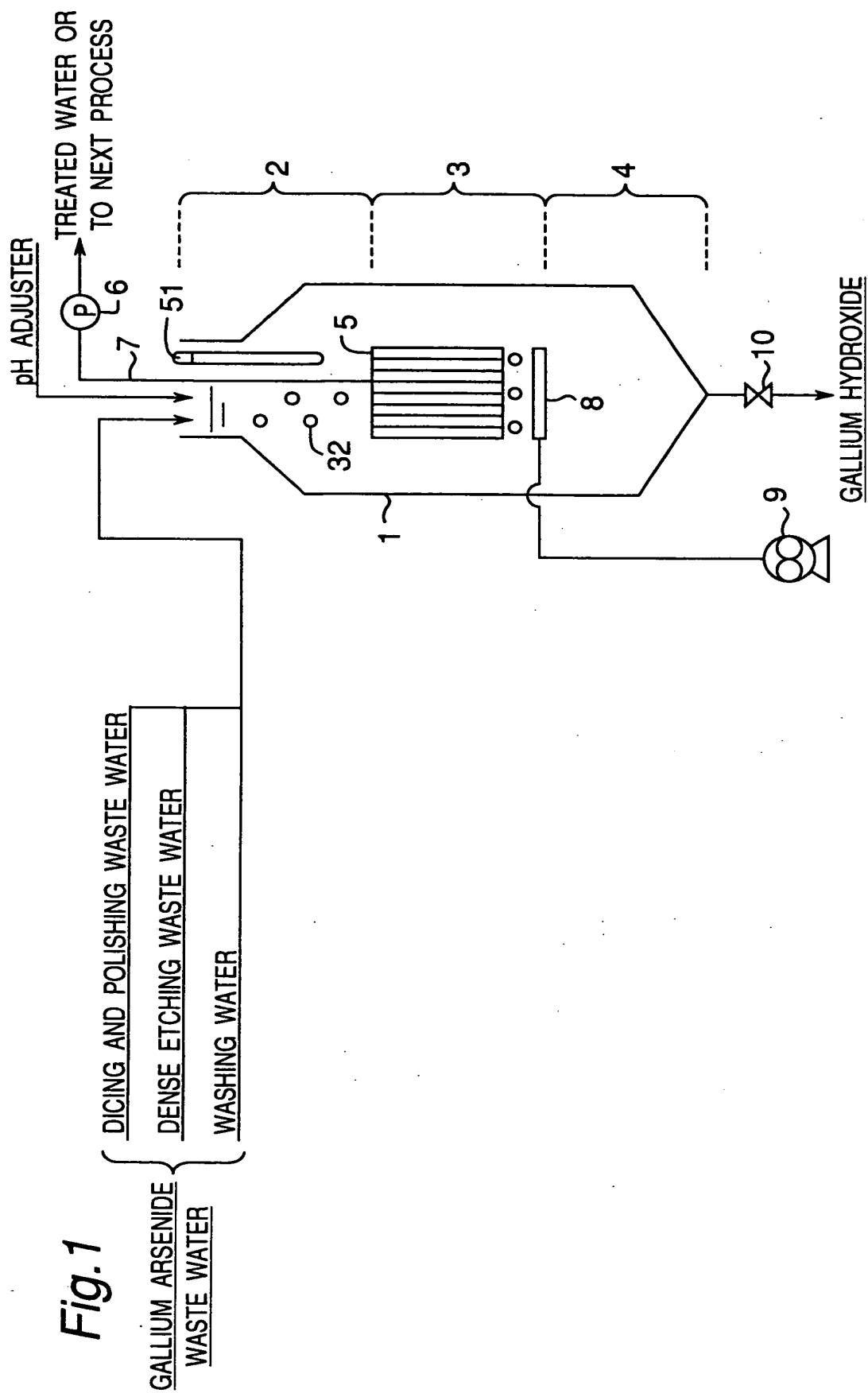


Fig. 1



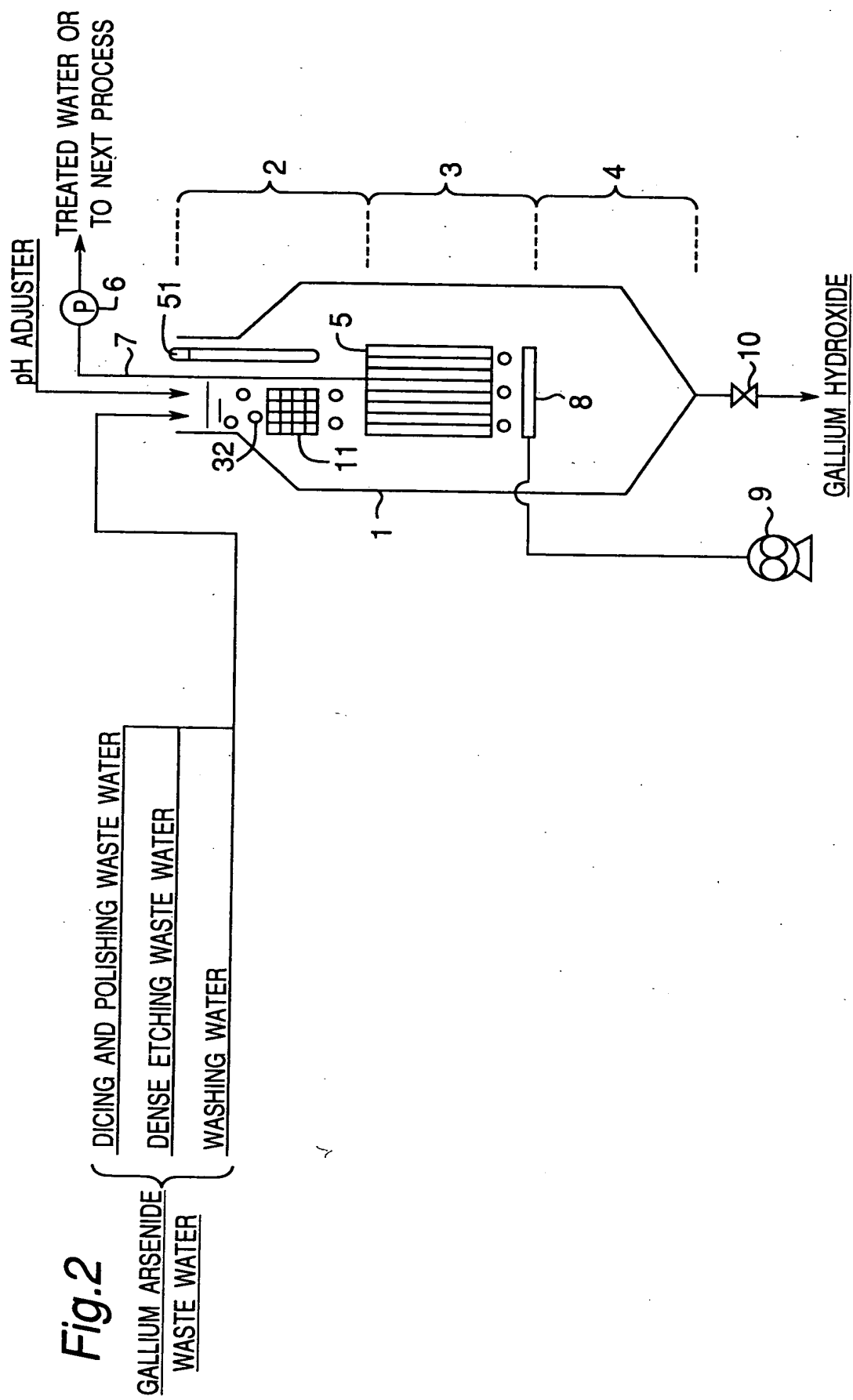


Fig.2

Fig.3

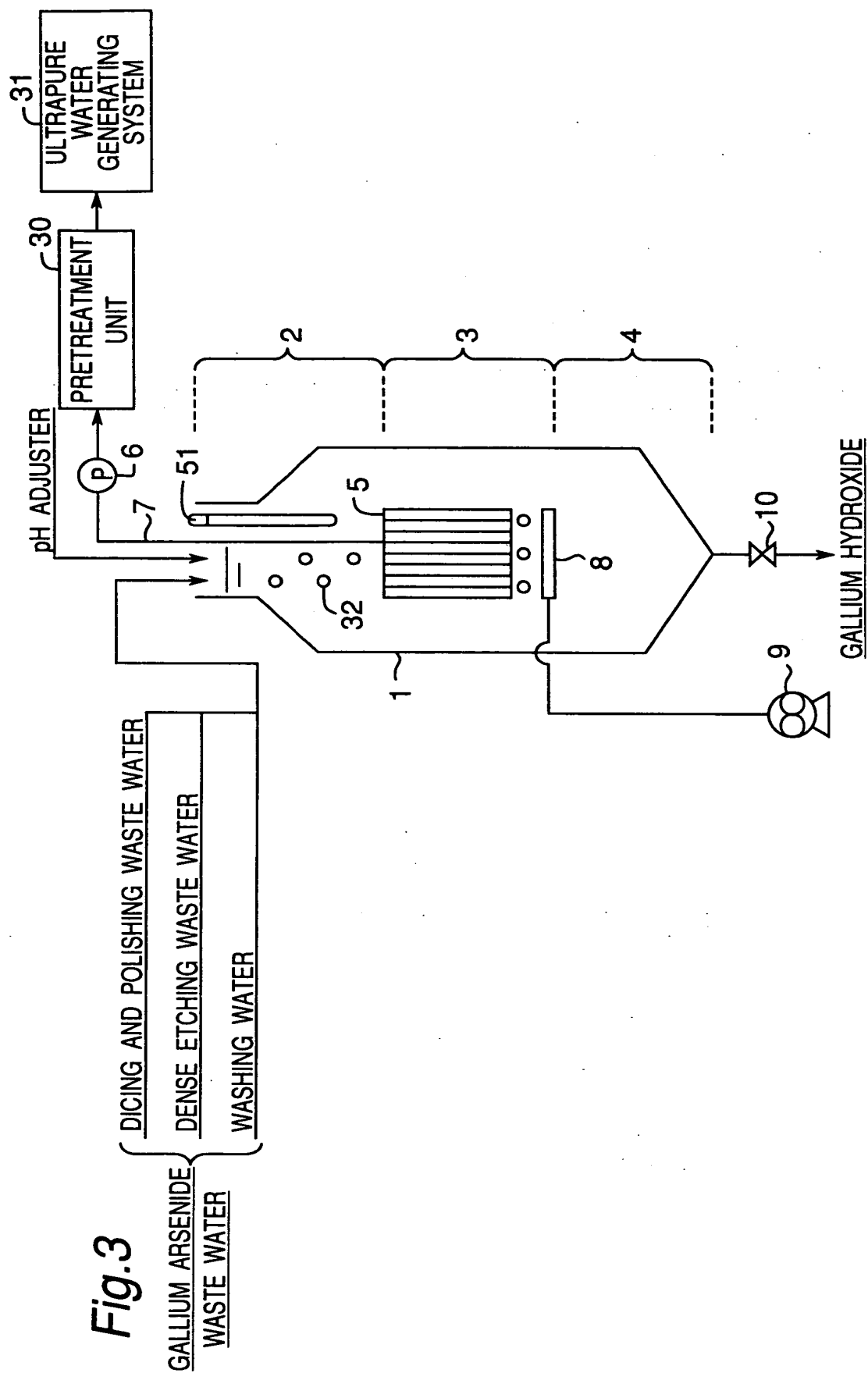


Fig.4

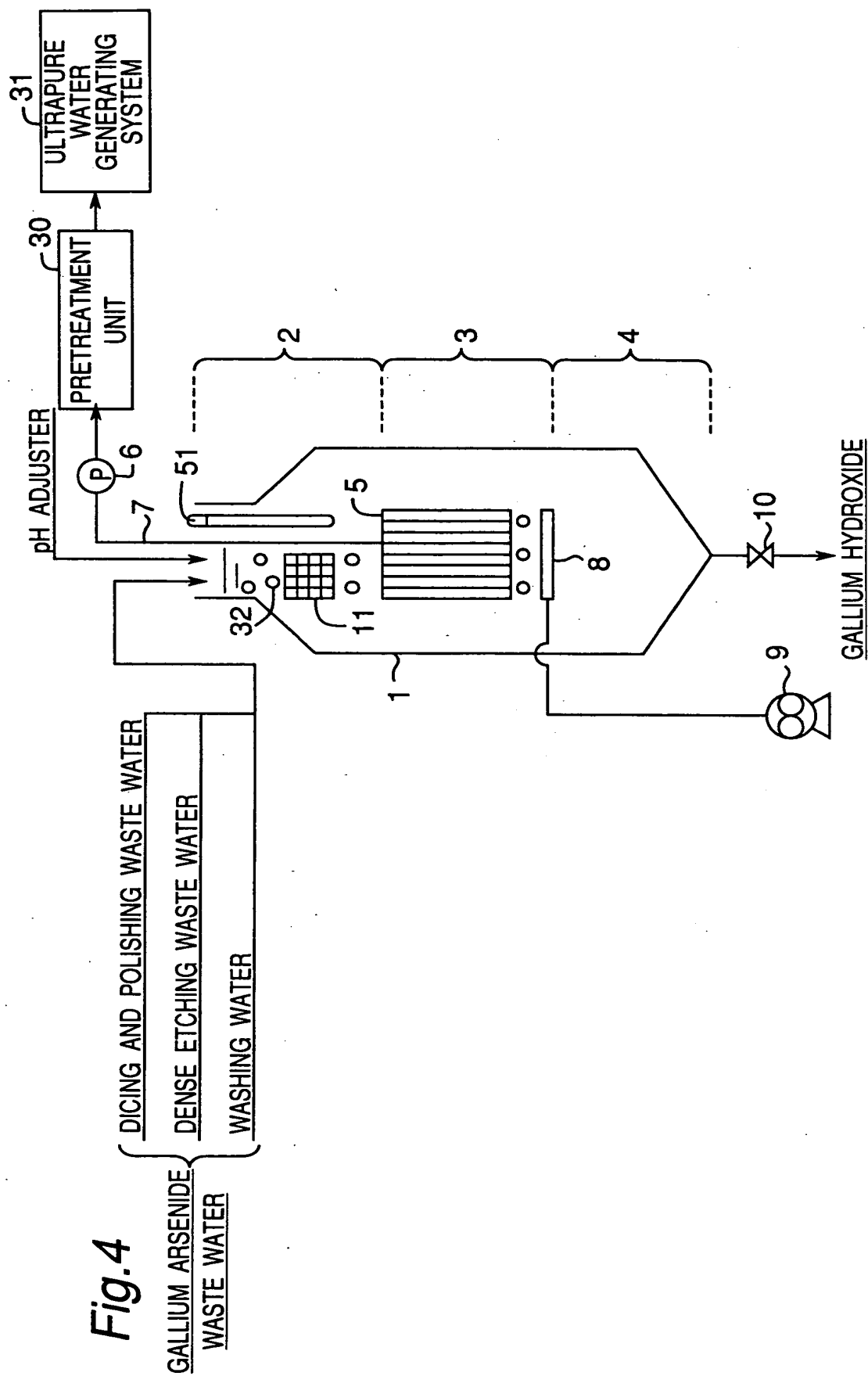


Fig.5

GALLIUM ARSENIDE
WASTE WATER

DICING AND POLISHING WASTE WATER
DENSE ETCHING WASTE WATER
WASHING WATER

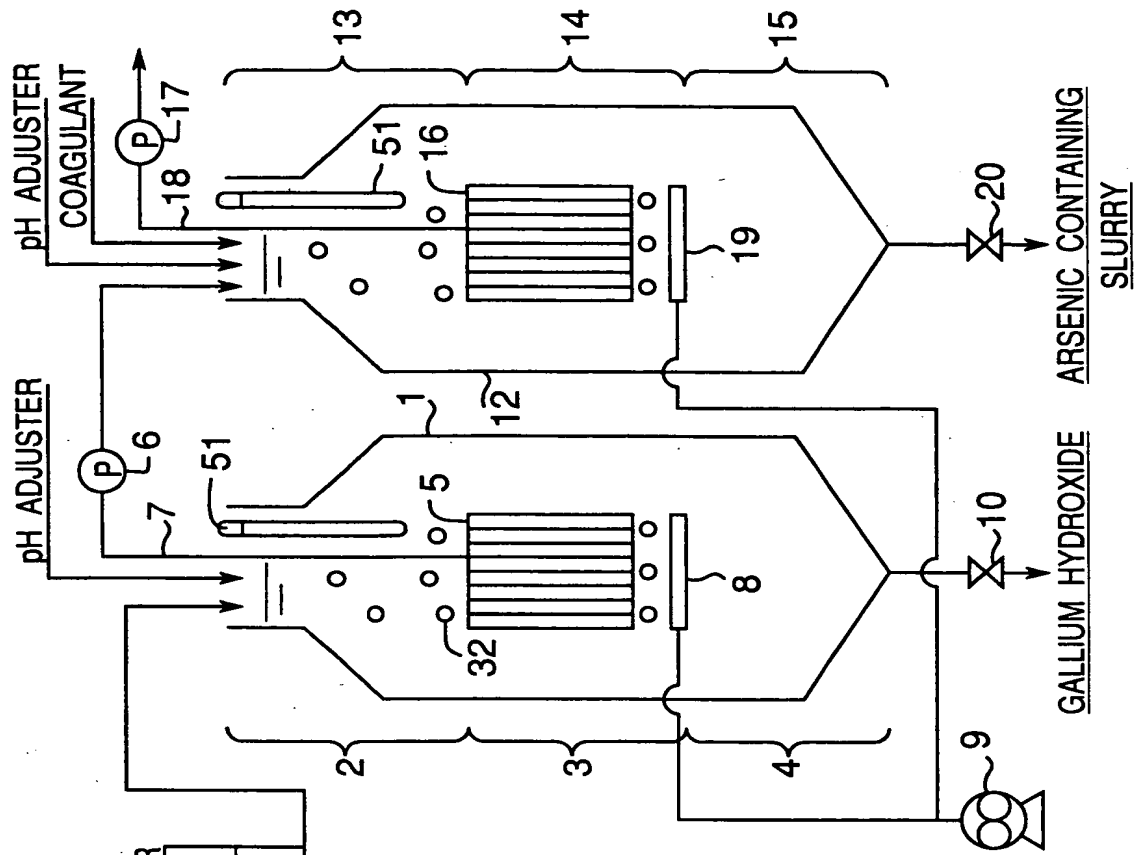


Fig.6

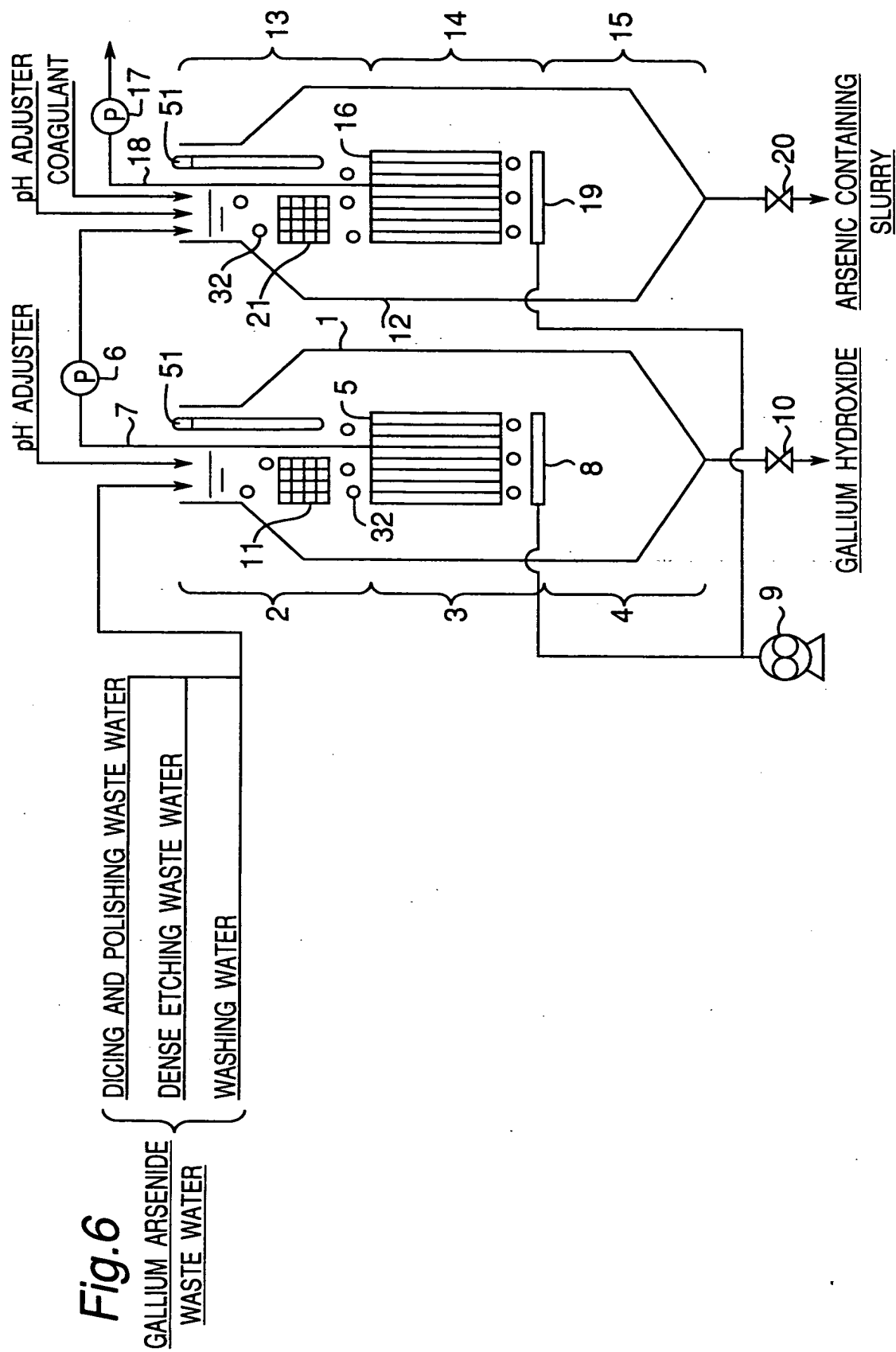


Fig. 7

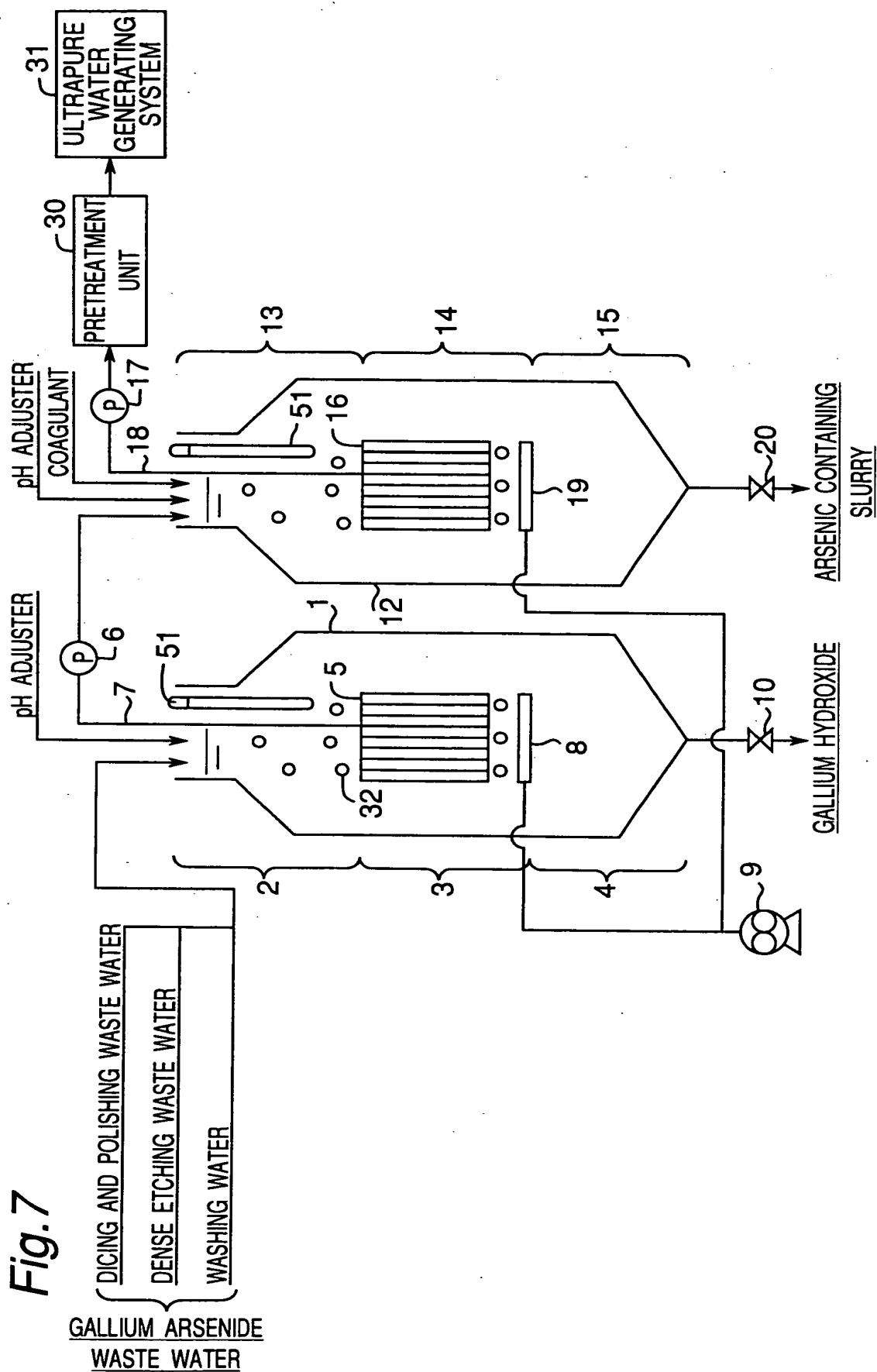


Fig. 8

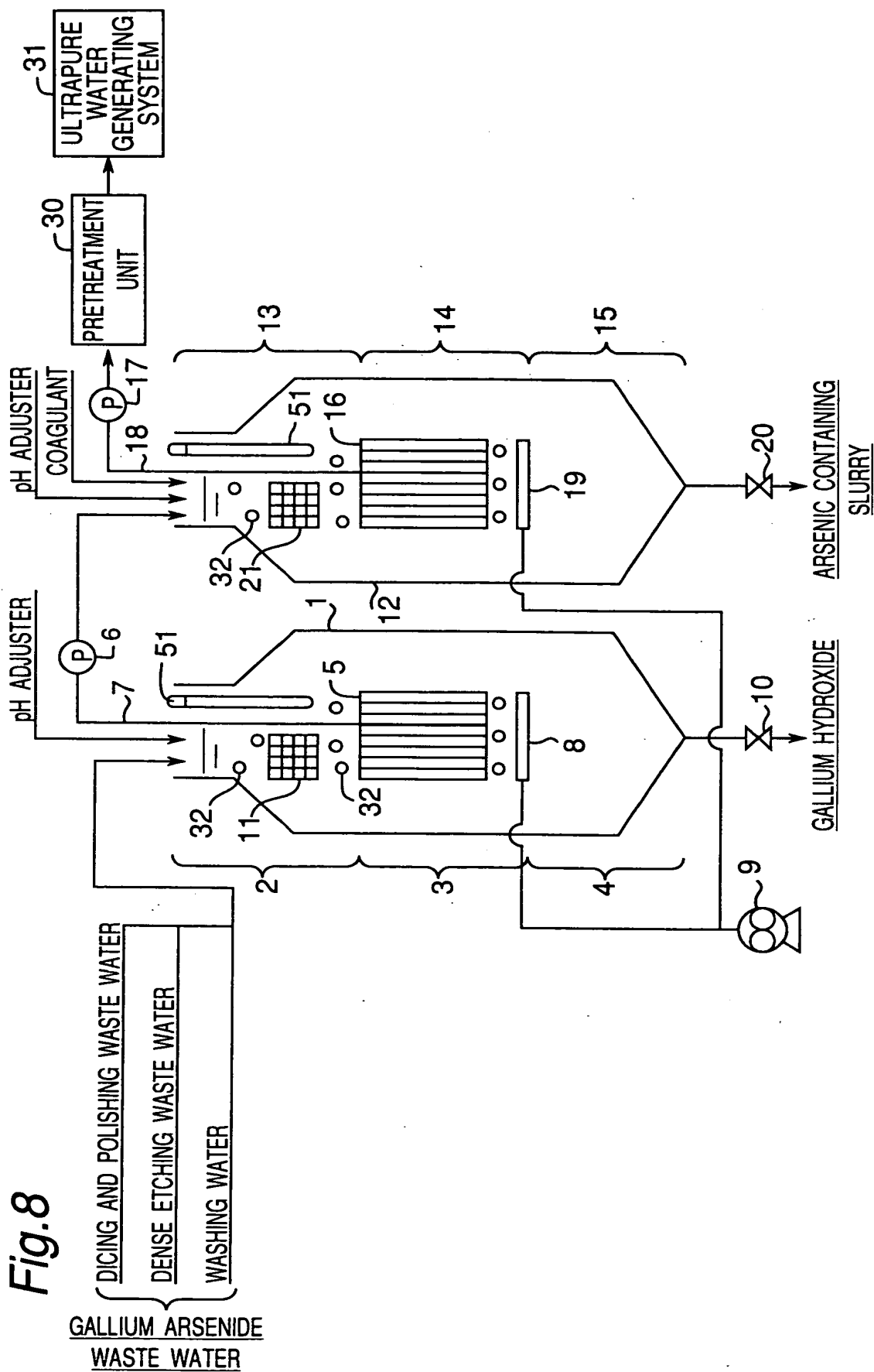


Fig. 9

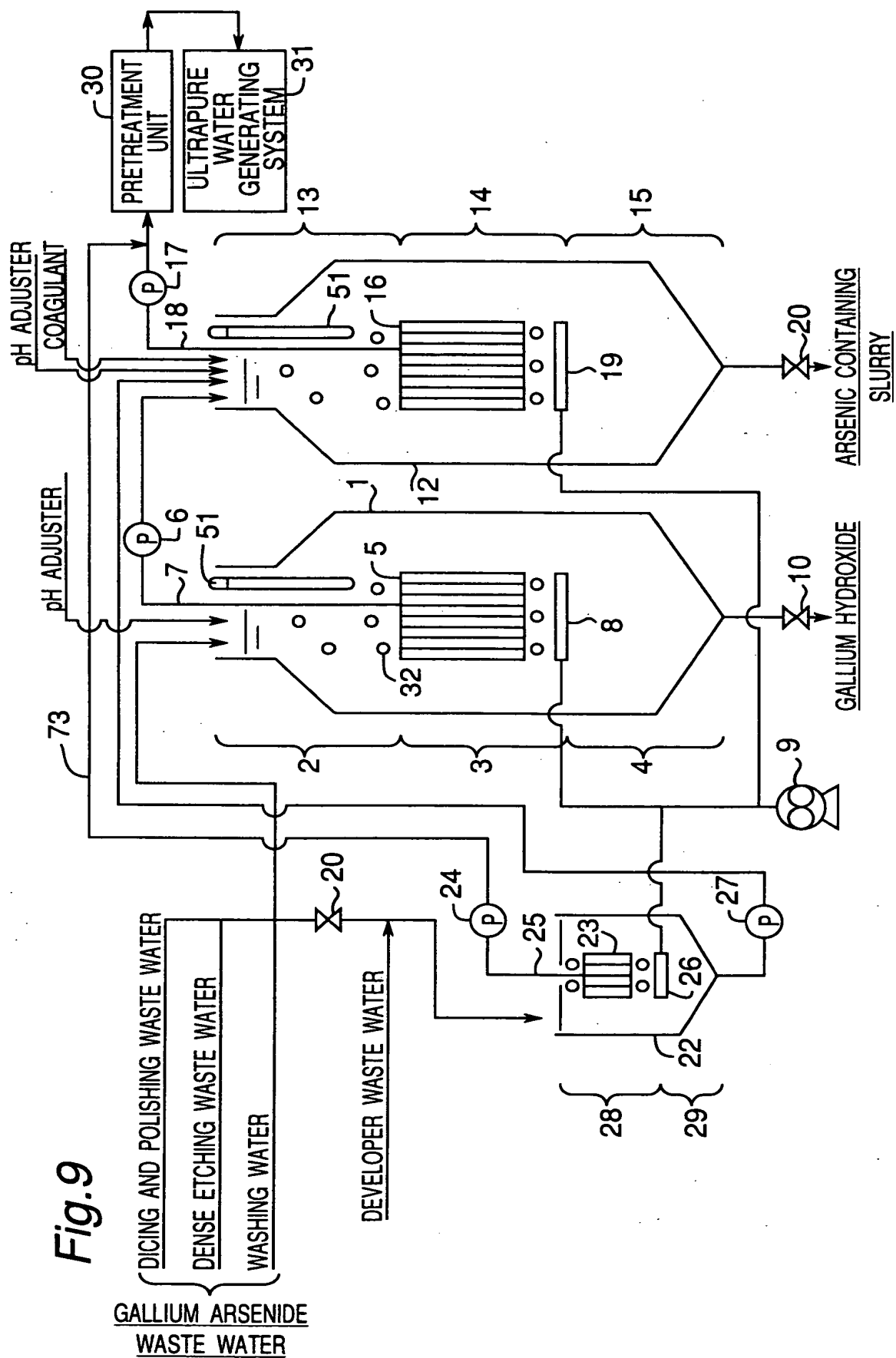


Fig. 10

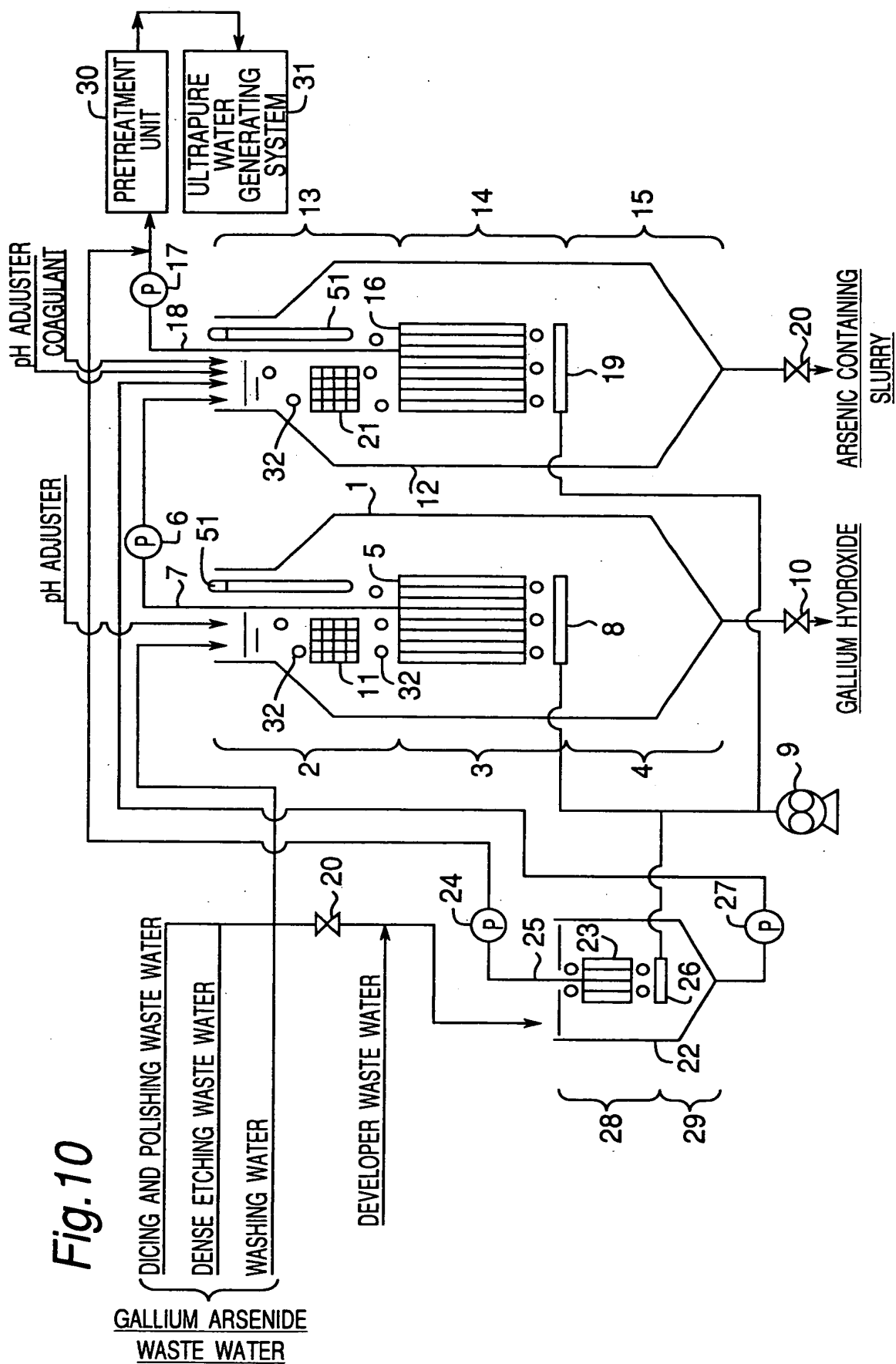


Fig. 11

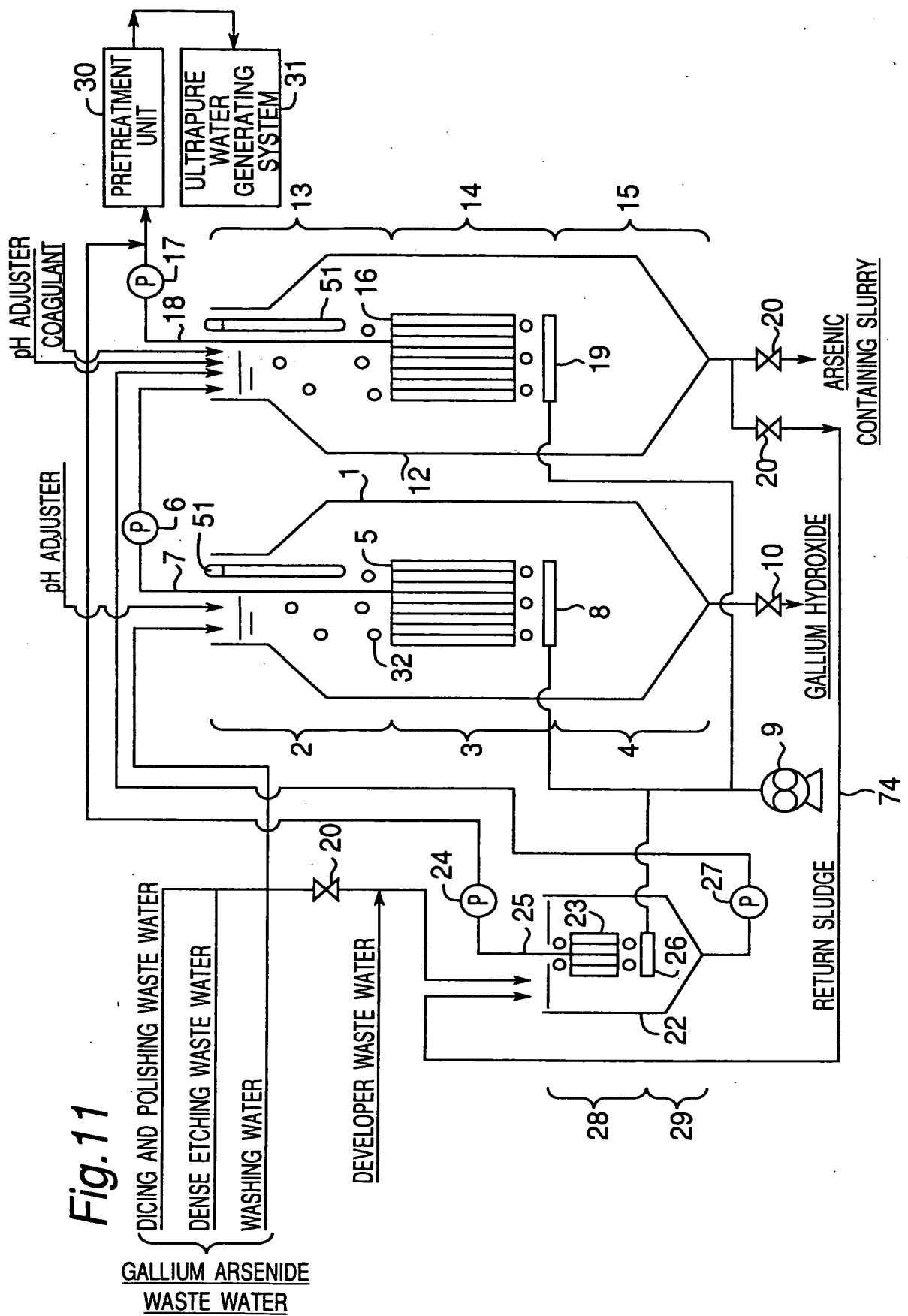


Fig. 12

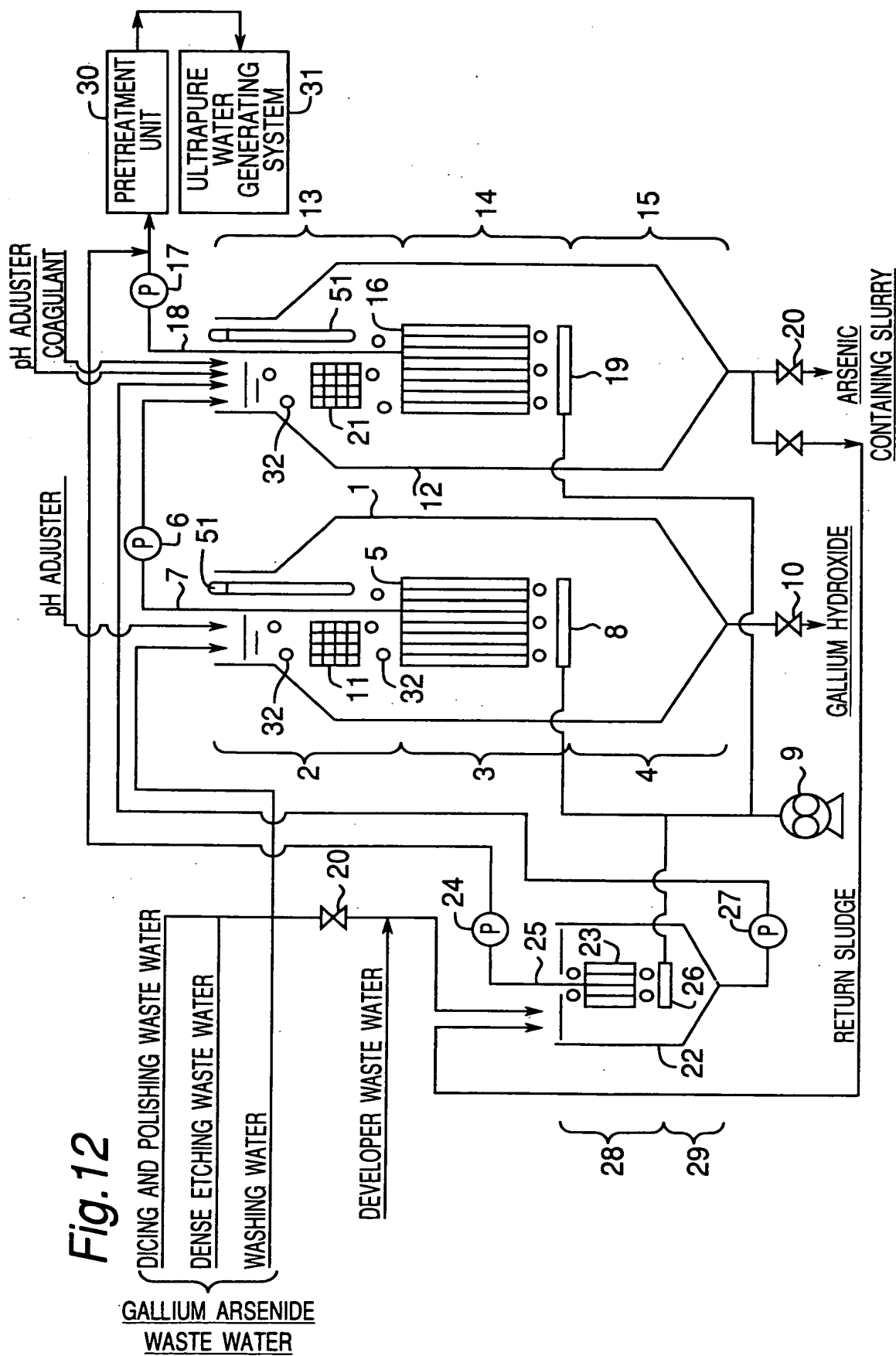


Fig. 13A

WHEN CONCENTRATIONS OF GALLIUM AND ARSENIC ARE NORMAL CONCENTRATIONS

[illegible]

Fig. 13B

WHEN CONCENTRATIONS OF GALLIUM AND ARSENIC ARE LOW CONCENTRATIONS

[illegible]

Fig. 14

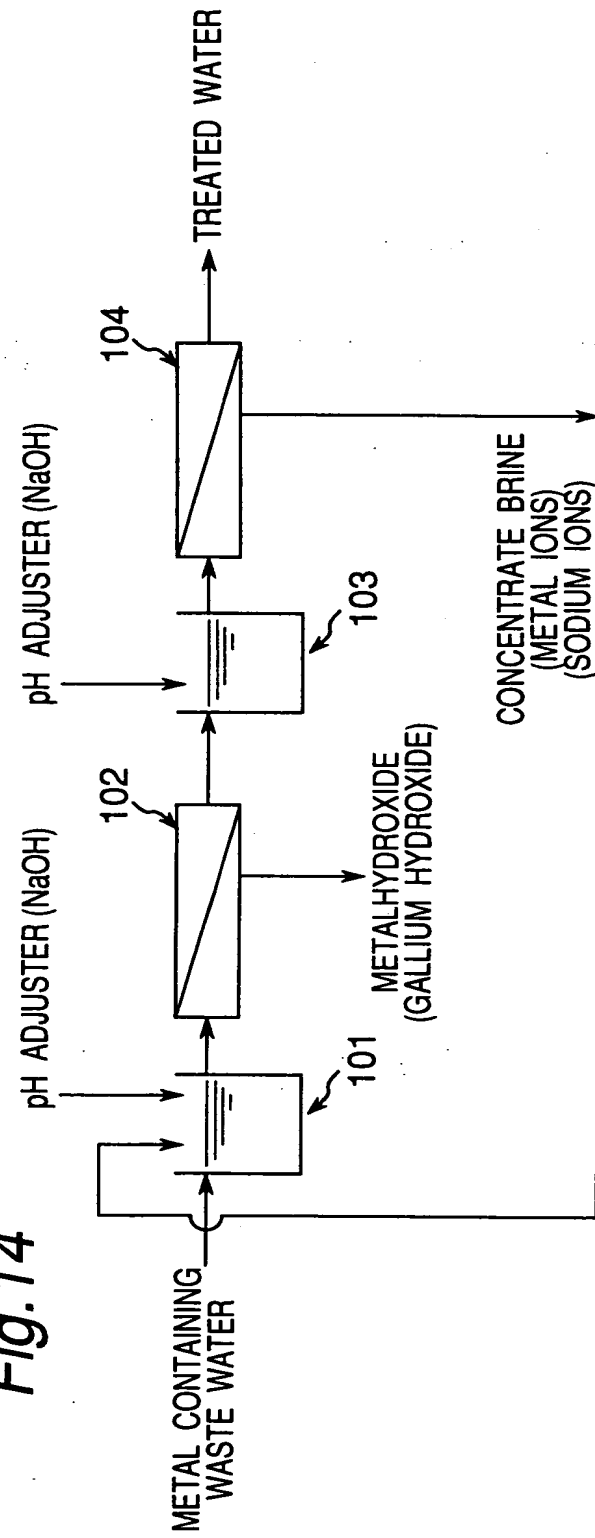


Fig. 15

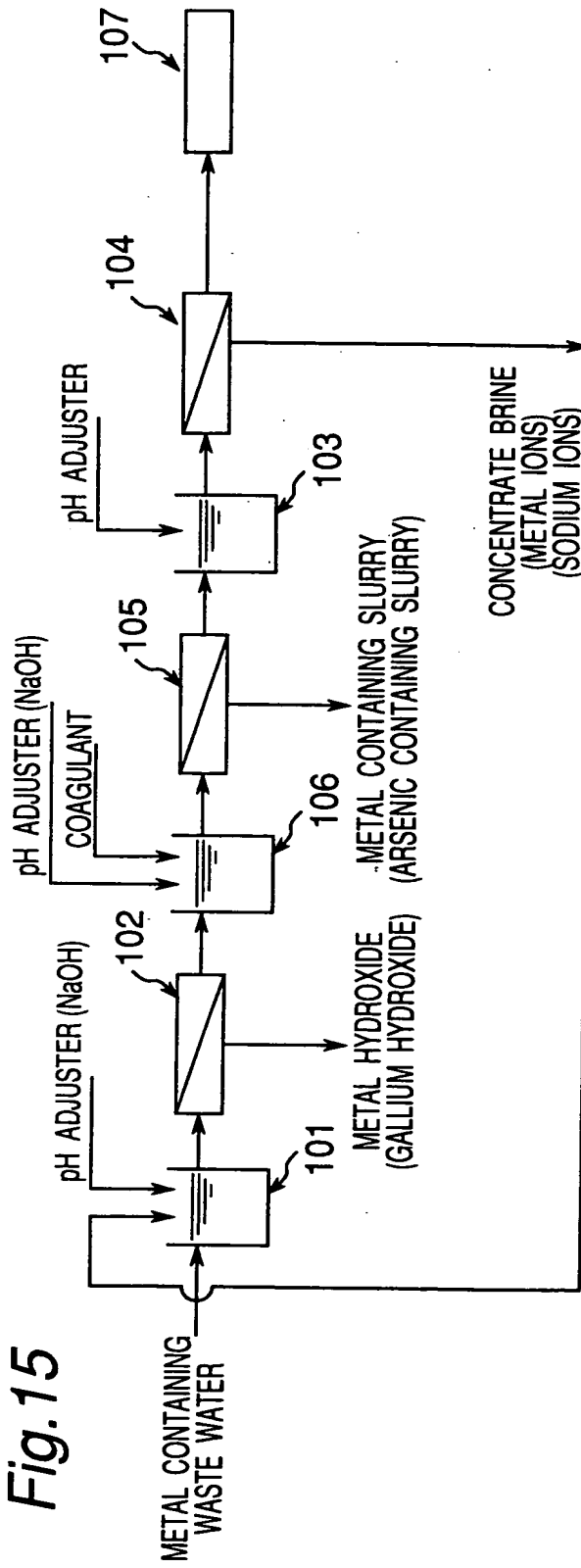


Fig. 16

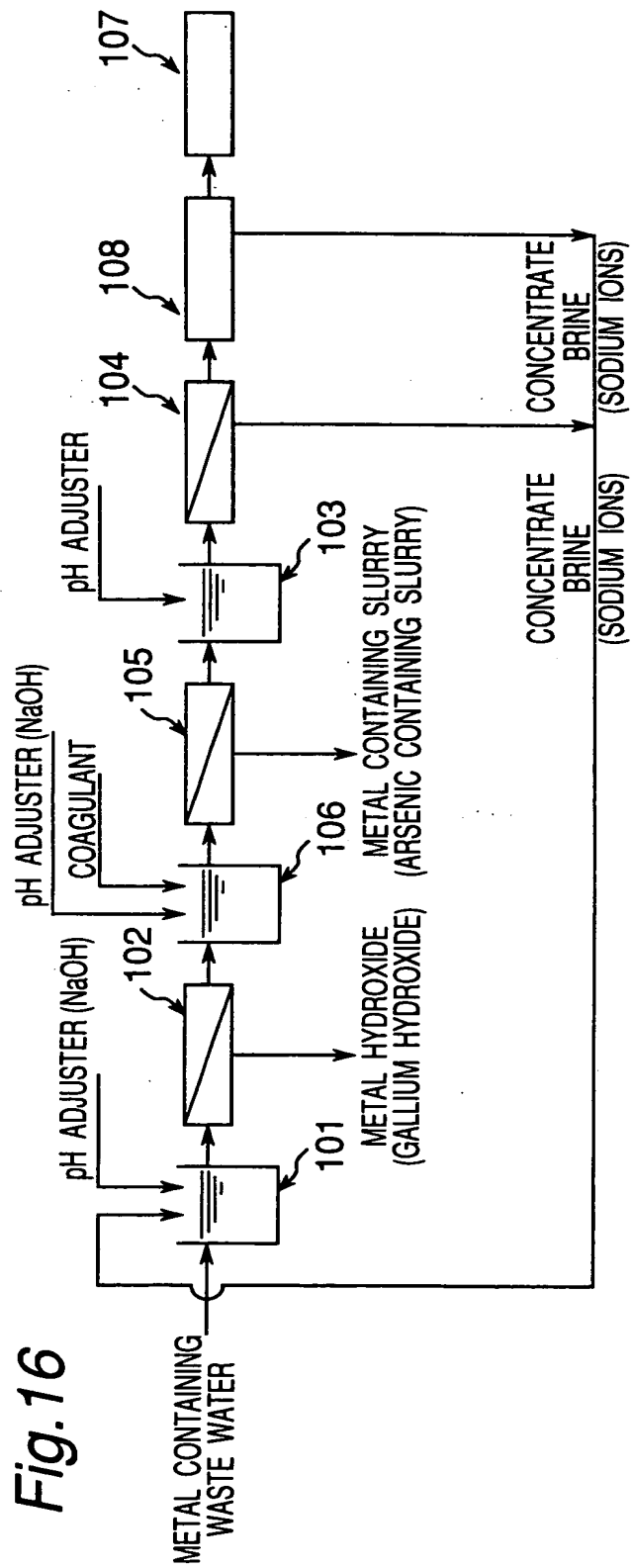


Fig. 17

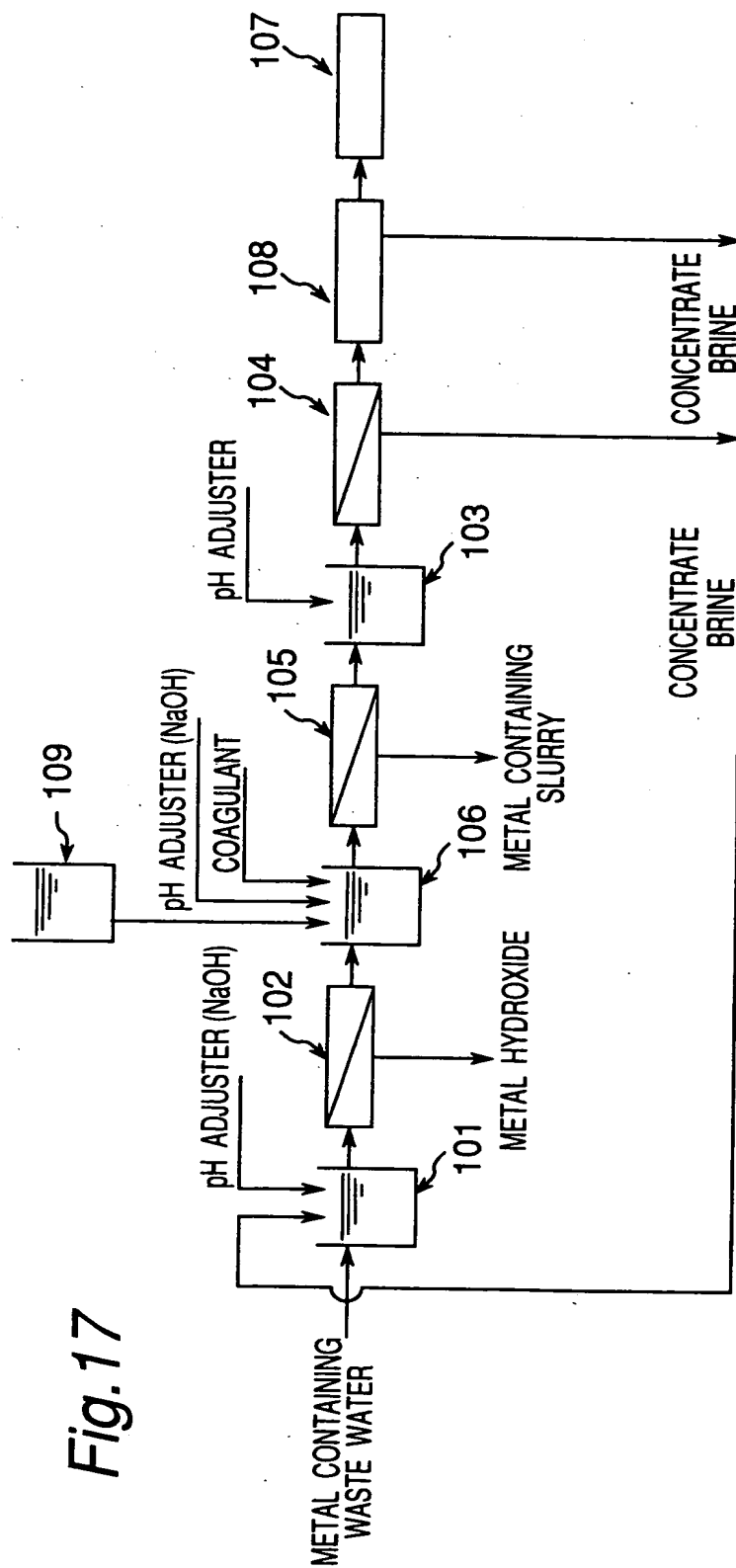


Fig.18

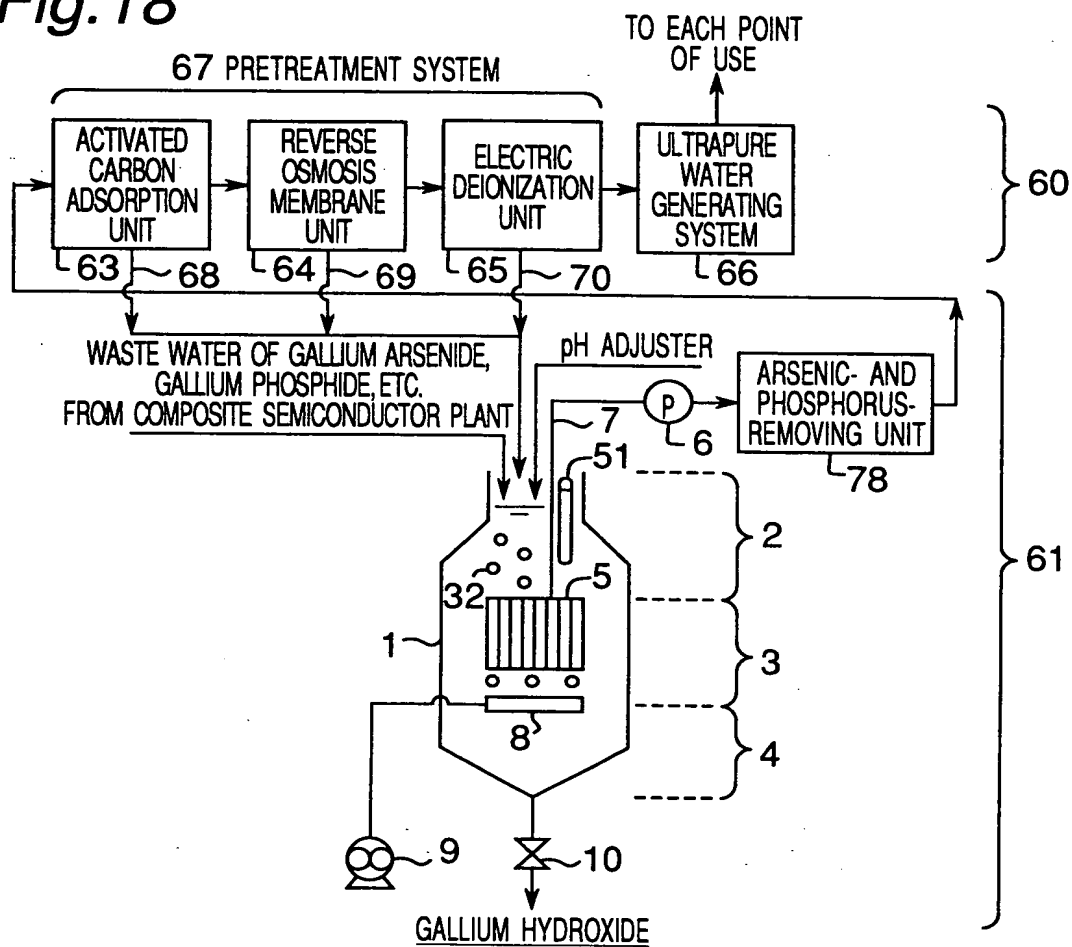


Fig. 19

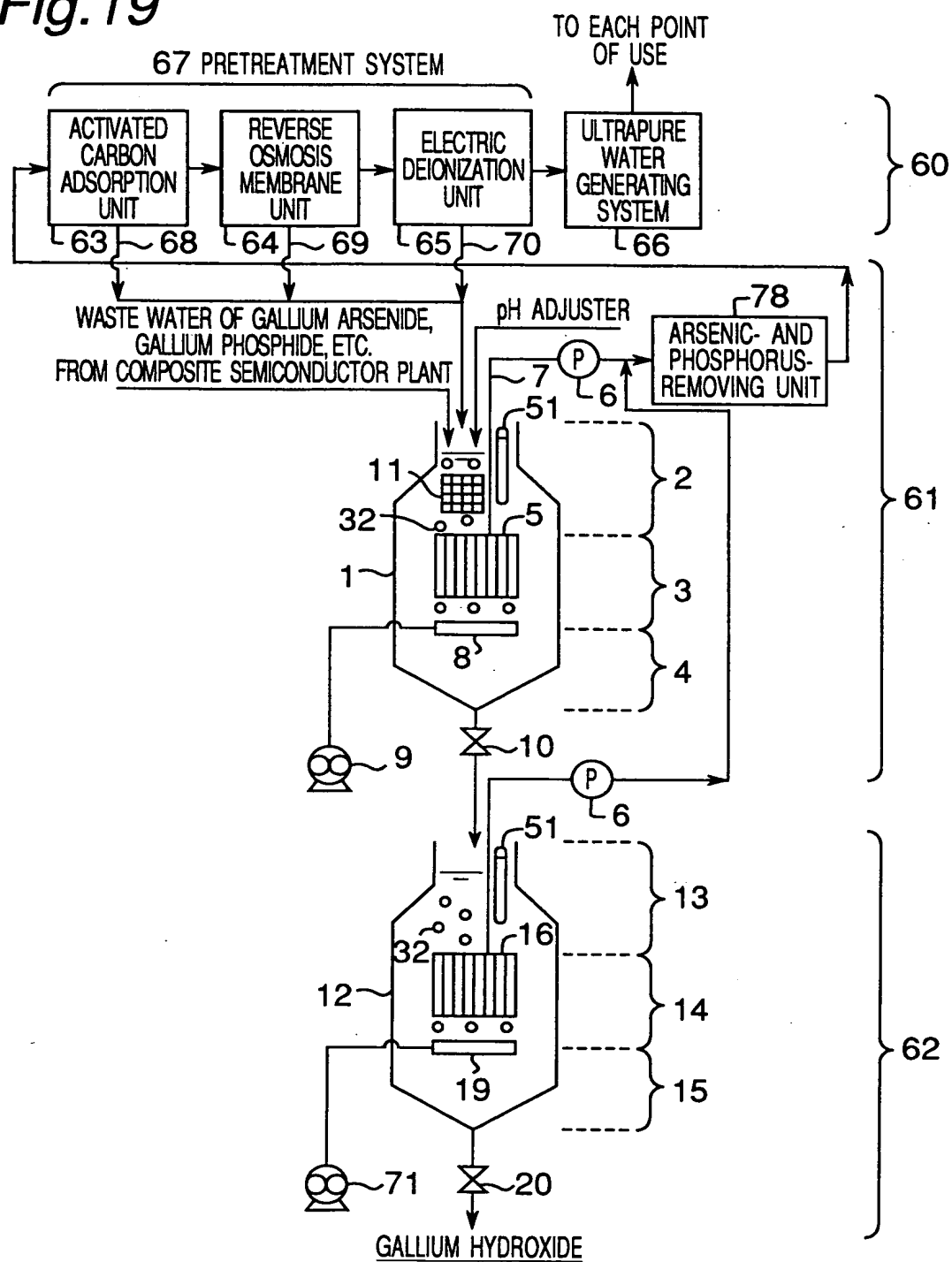


Fig.20

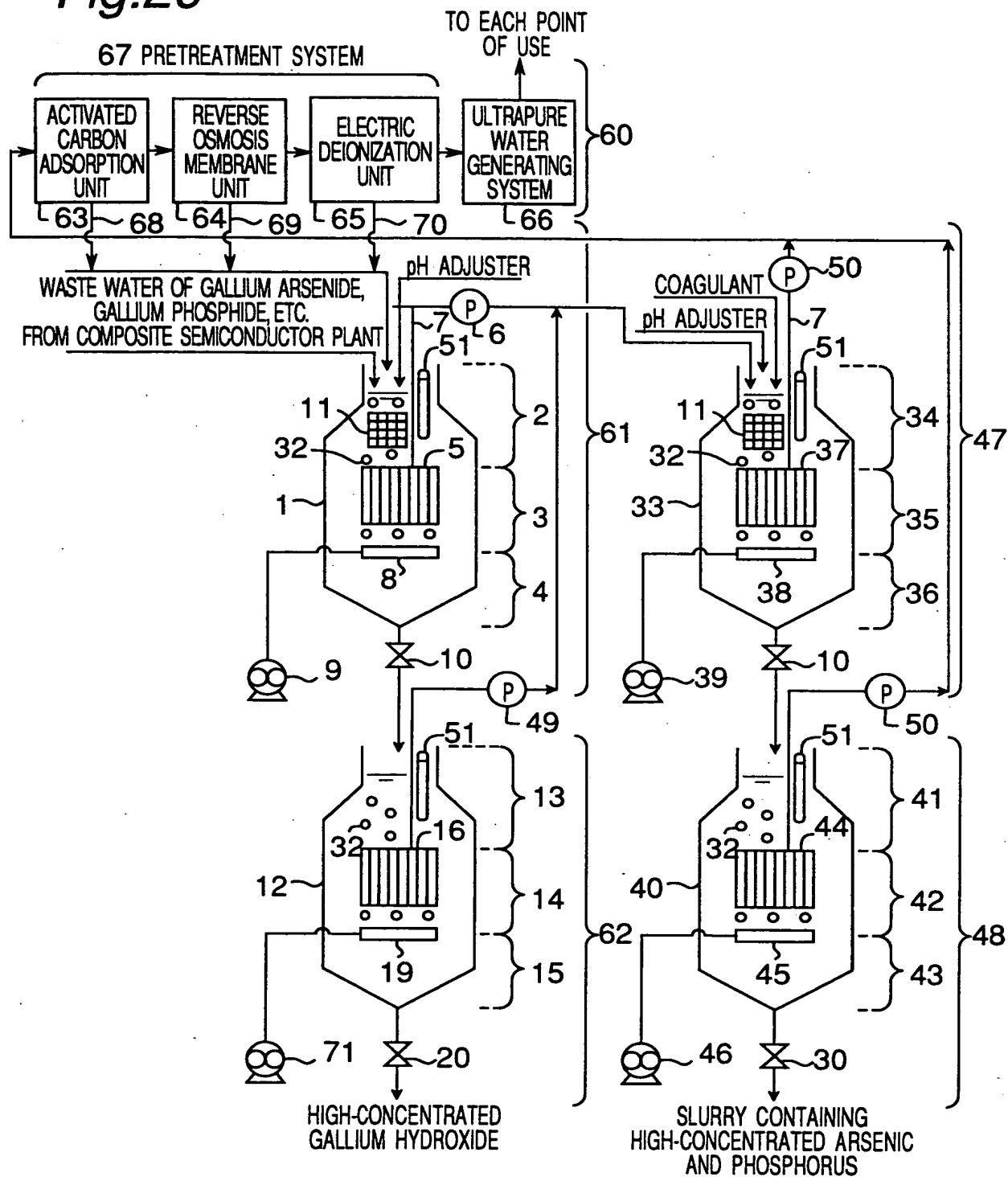


Fig.21

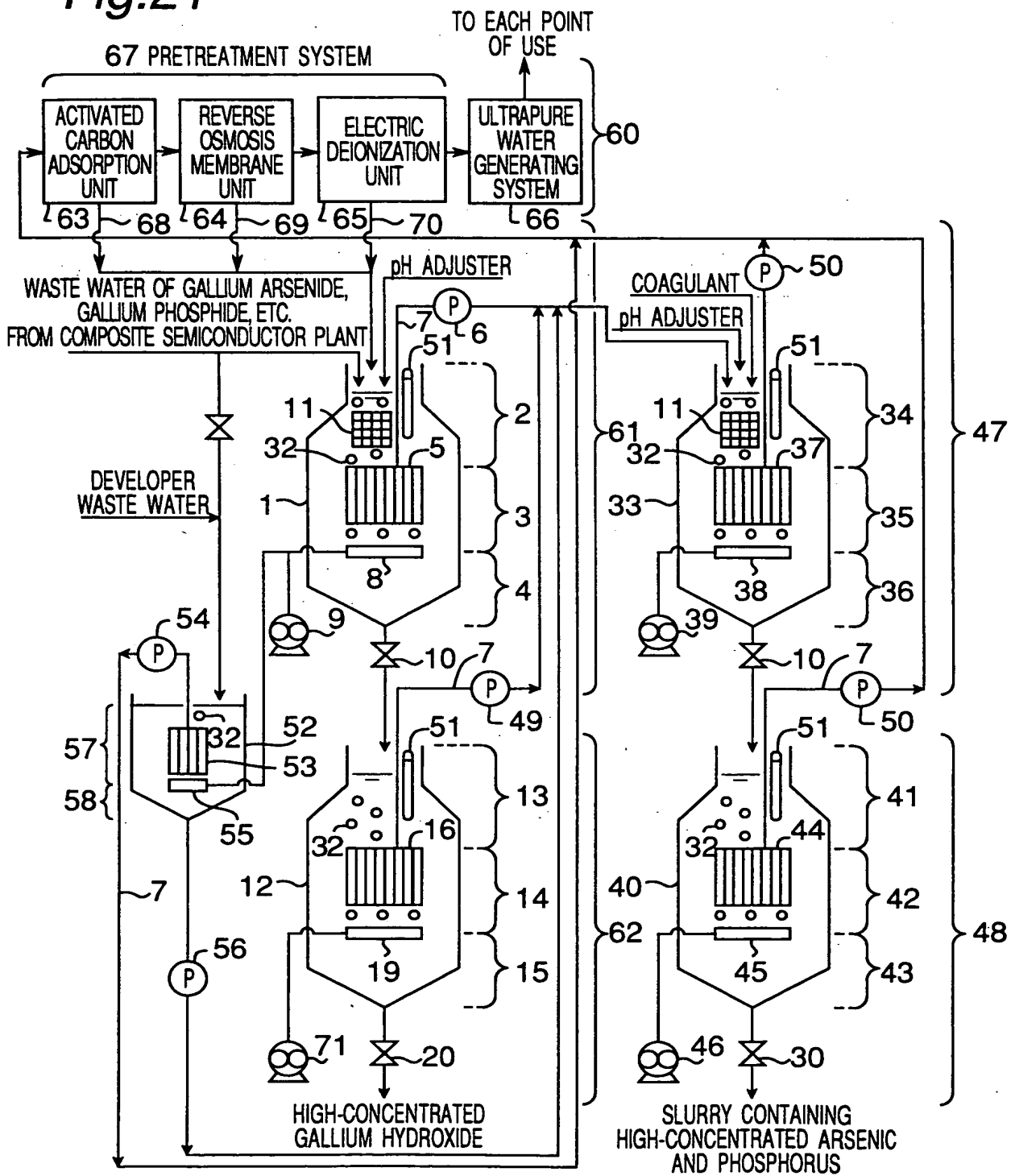


Fig.22

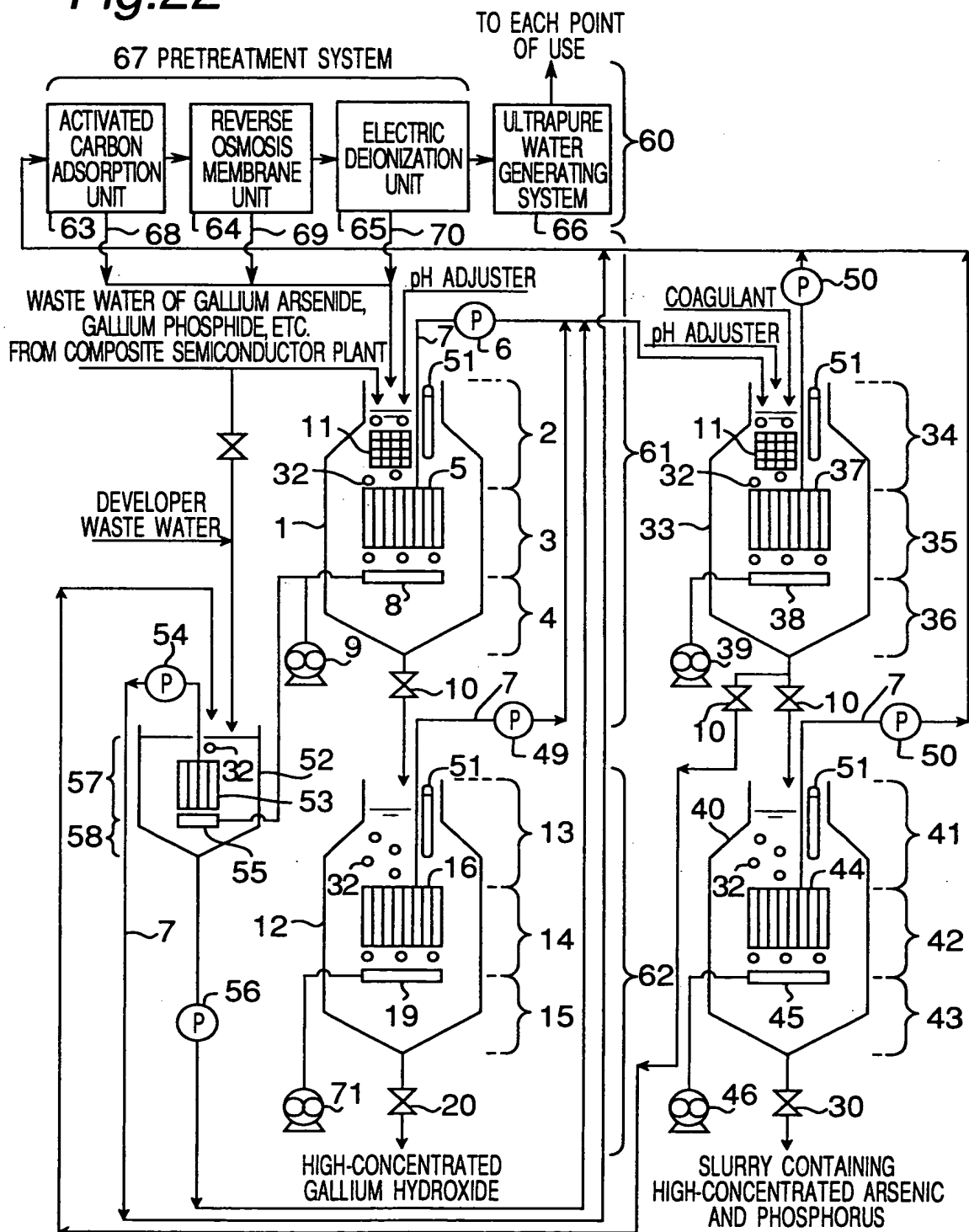


Fig.23

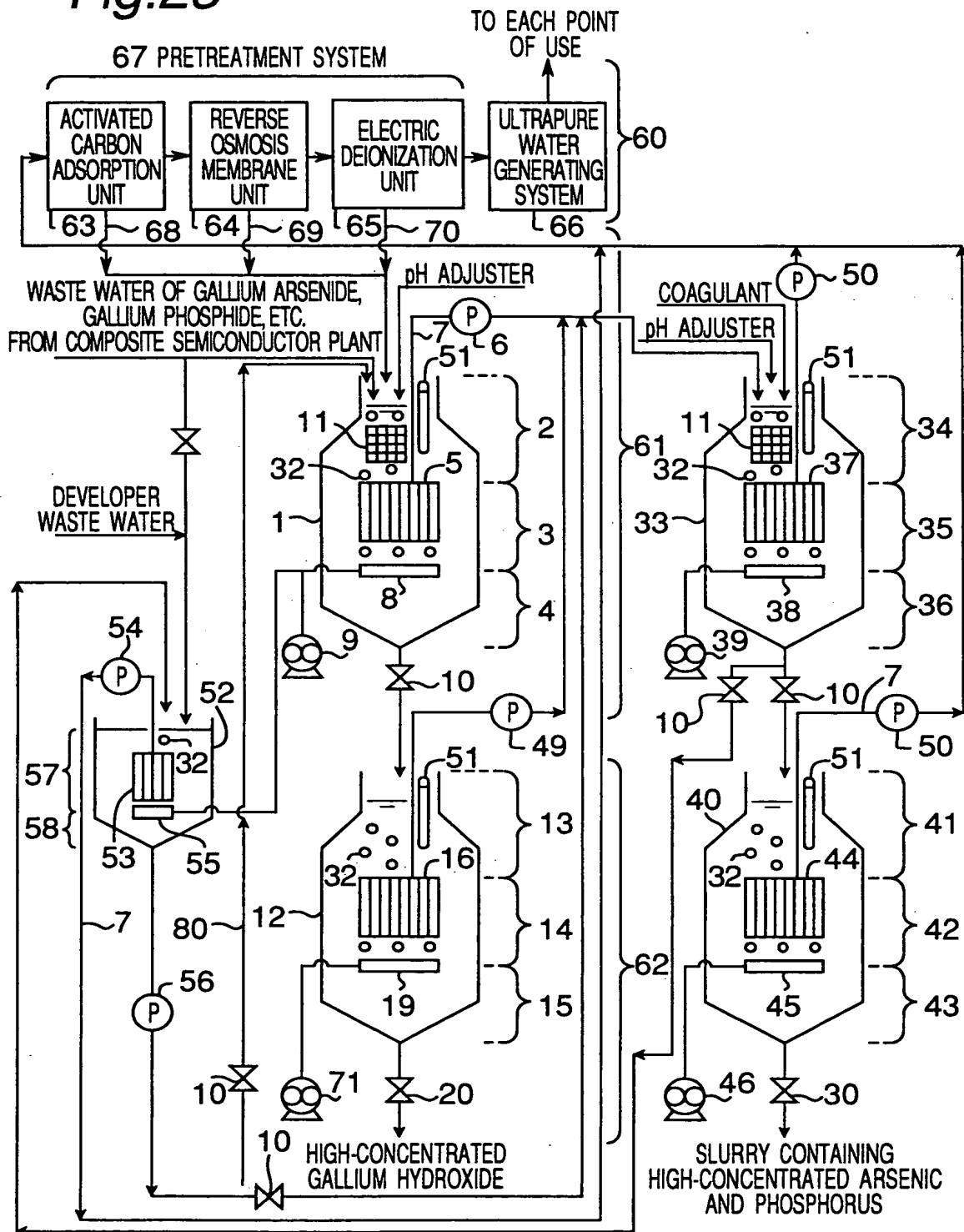


Fig.24

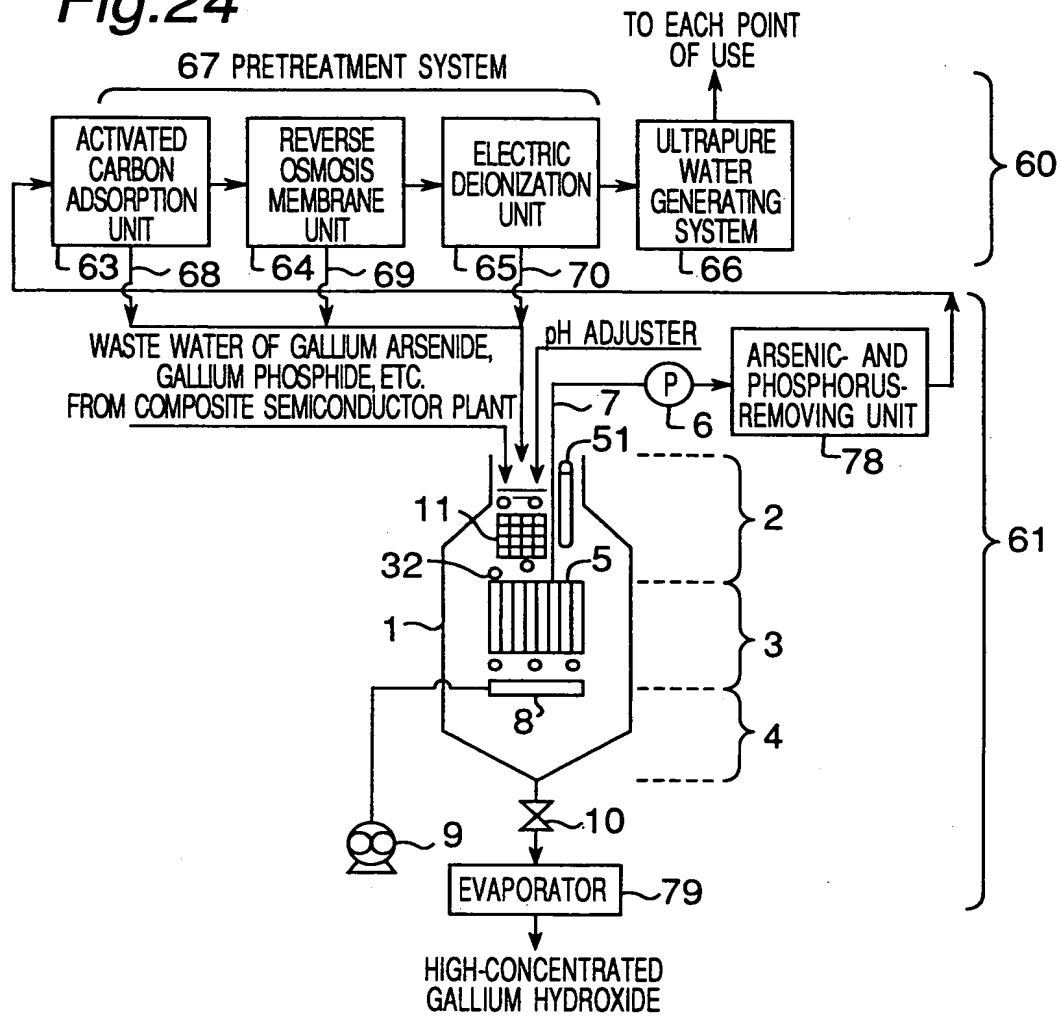


Fig.25

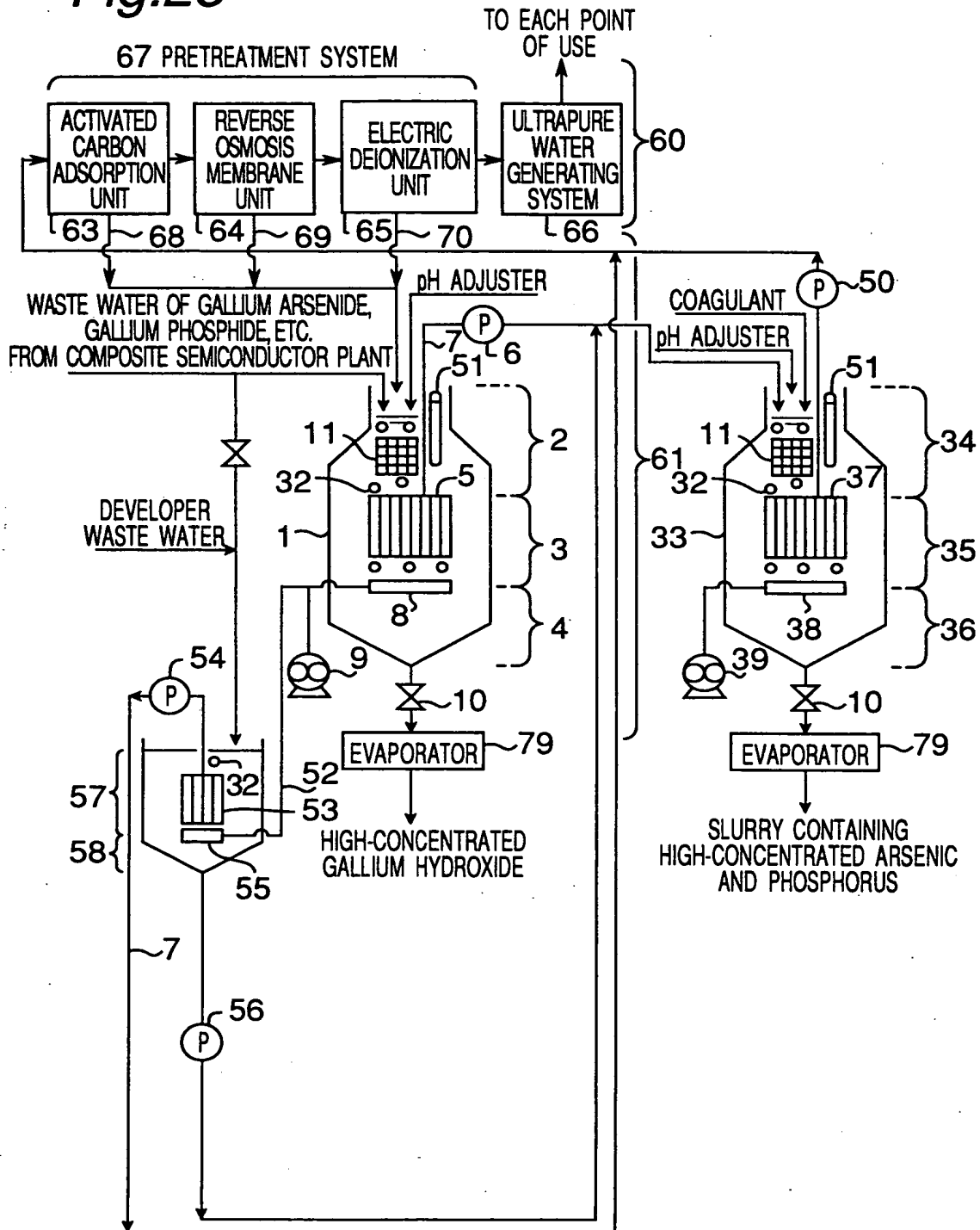


Fig.26

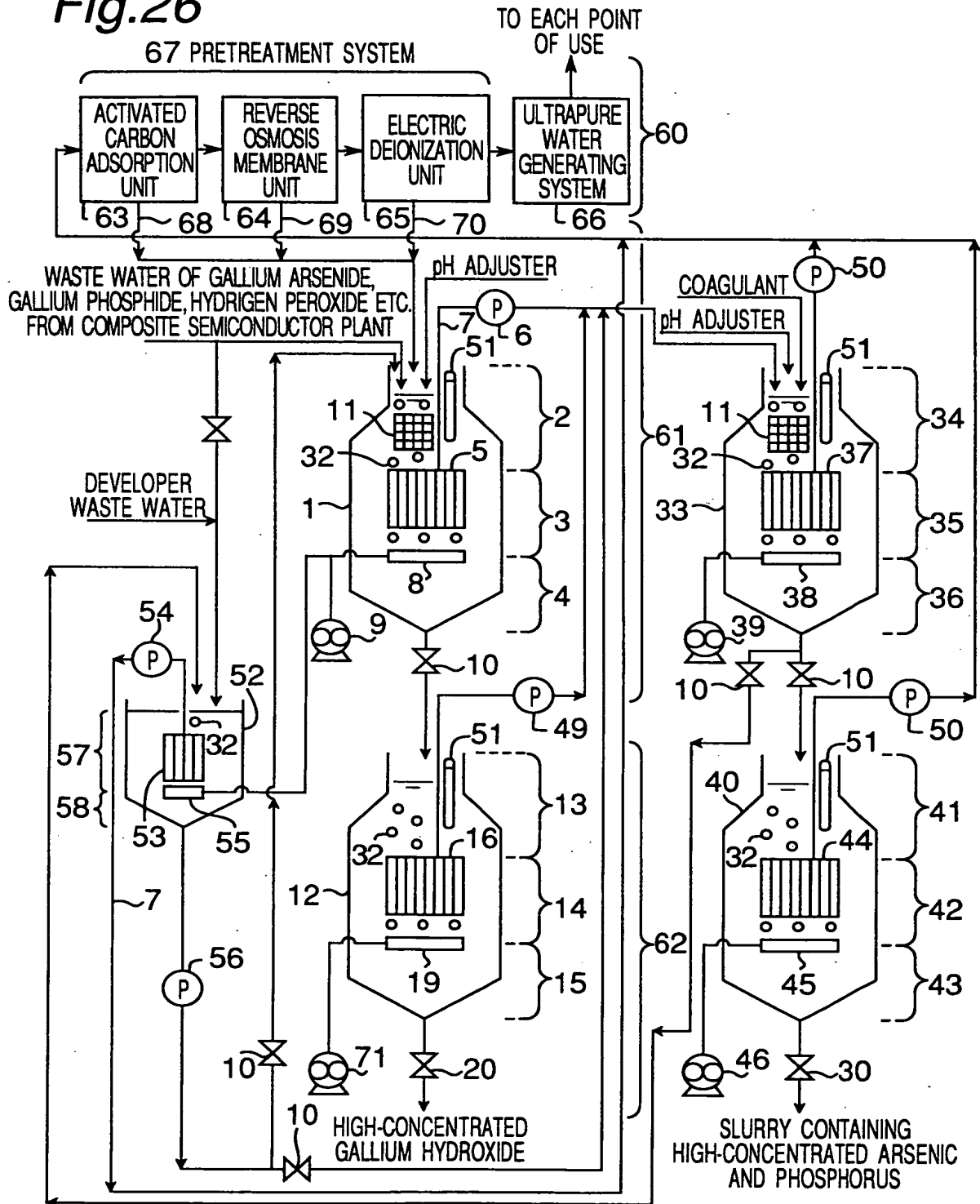


Fig.27A

WHEN CONCENTRATIONS OF GALLIUM AND ARSENIC ARE NORMAL CONCENTRATIONS

TANK NAME	RESIDENCE TIME	TIMING (RESIDENCE TIME)														
		1 HR.	2 HR.	3 HR.	4 HR.	5 HR.	6 HR.	7 HR.	8 HR.	9 HR.	10 HR.	11 HR.	12 HR.	13 HR.	14 HR.	15 HR.
SUBMERGED MEMBRANE SEPARATION TANK	1 HR.	—														
SECOND SUBMERGED MEMBRANE SEPARATION TANK	2 HR.		—	—												
THIRD SUBMERGED MEMBRANE SEPARATION TANK	4 HR.				—	—	—	—								
FOURTH SUBMERGED MEMBRANE SEPARATION TANK	4 HR.								—	—	—	—				

Fig.27B

WHEN CONCENTRATIONS OF GALLIUM AND ARSENIC ARE LOW CONCENTRATIONS

TANK NAME	RESIDENCE TIME	TIMING (RESIDENCE TIME)														
		1 HR.	2 HR.	3 HR.	4 HR.	5 HR.	6 HR.	7 HR.	8 HR.	9 HR.	10 HR.	11 HR.	12 HR.	13 HR.	14 HR.	15 HR.
SUBMERGED MEMBRANE SEPARATION TANK	1 HR.	—														
SECOND SUBMERGED MEMBRANE SEPARATION TANK	2 HR.		—	—												
THIRD SUBMERGED MEMBRANE SEPARATION TANK	3 HR.				—	—	—									
FOURTH SUBMERGED MEMBRANE SEPARATION TANK	3 HR.							—	—	—						

Fig. 28A

WHEN CONCENTRATIONS OF GALLIUM AND ARSENIC ARE NORMAL CONCENTRATIONS

[illegible]

Fig. 28B

WHEN CONCENTRATIONS OF GALLIUM AND ARSENIC ARE LOW CONCENTRATIONS

[illegible]

Fig.29

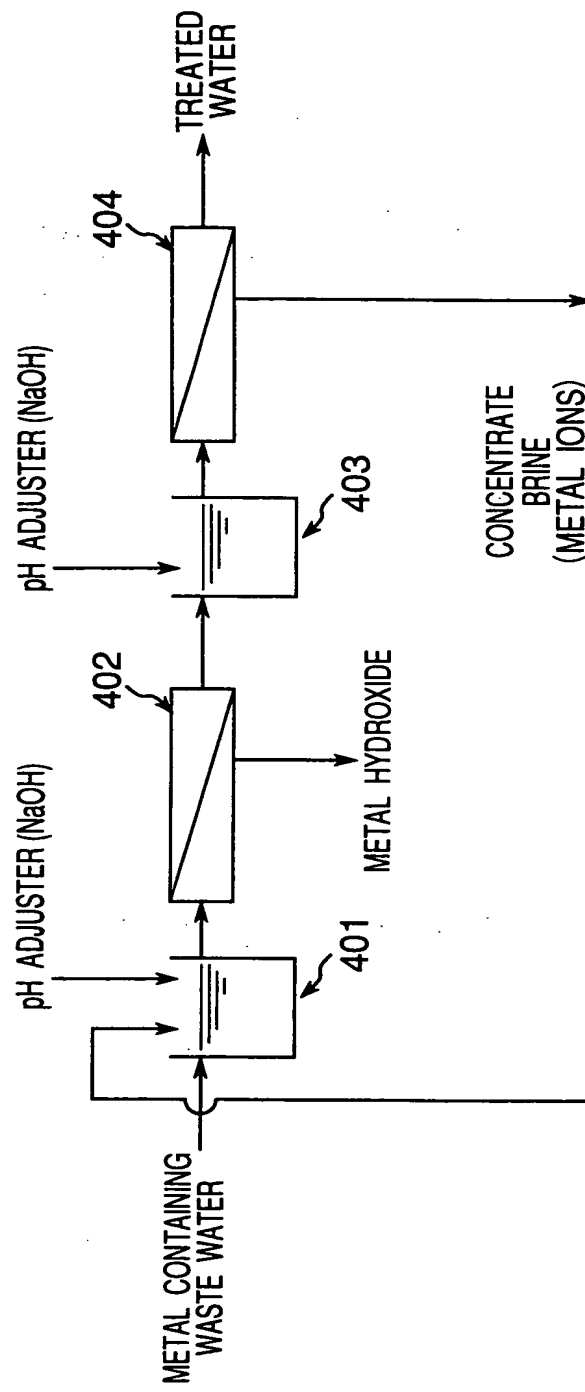


Fig.30

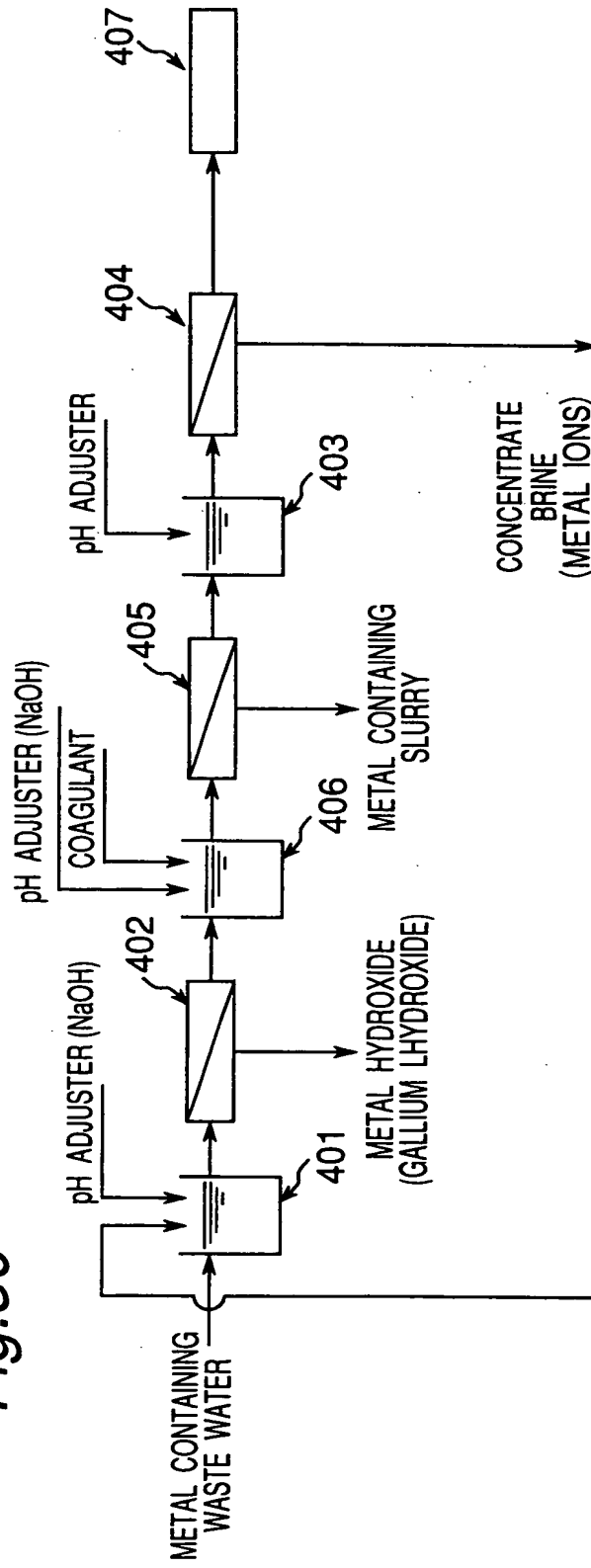


Fig.31

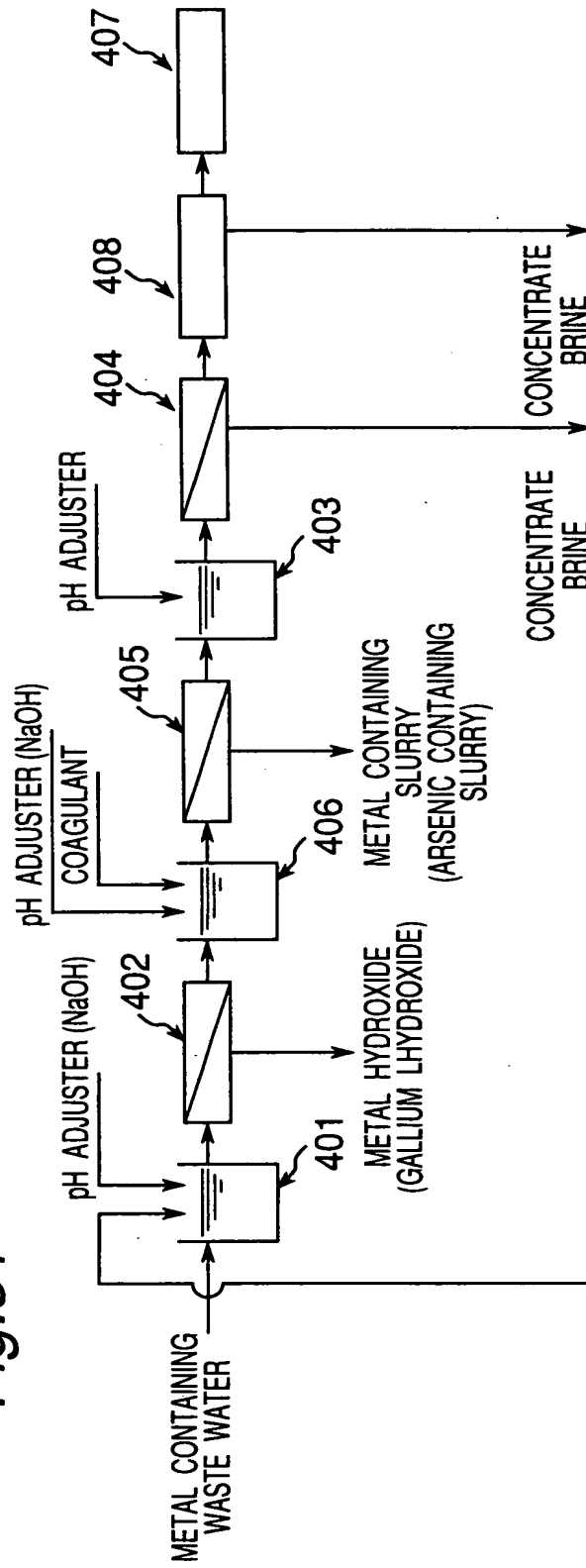


Fig.32

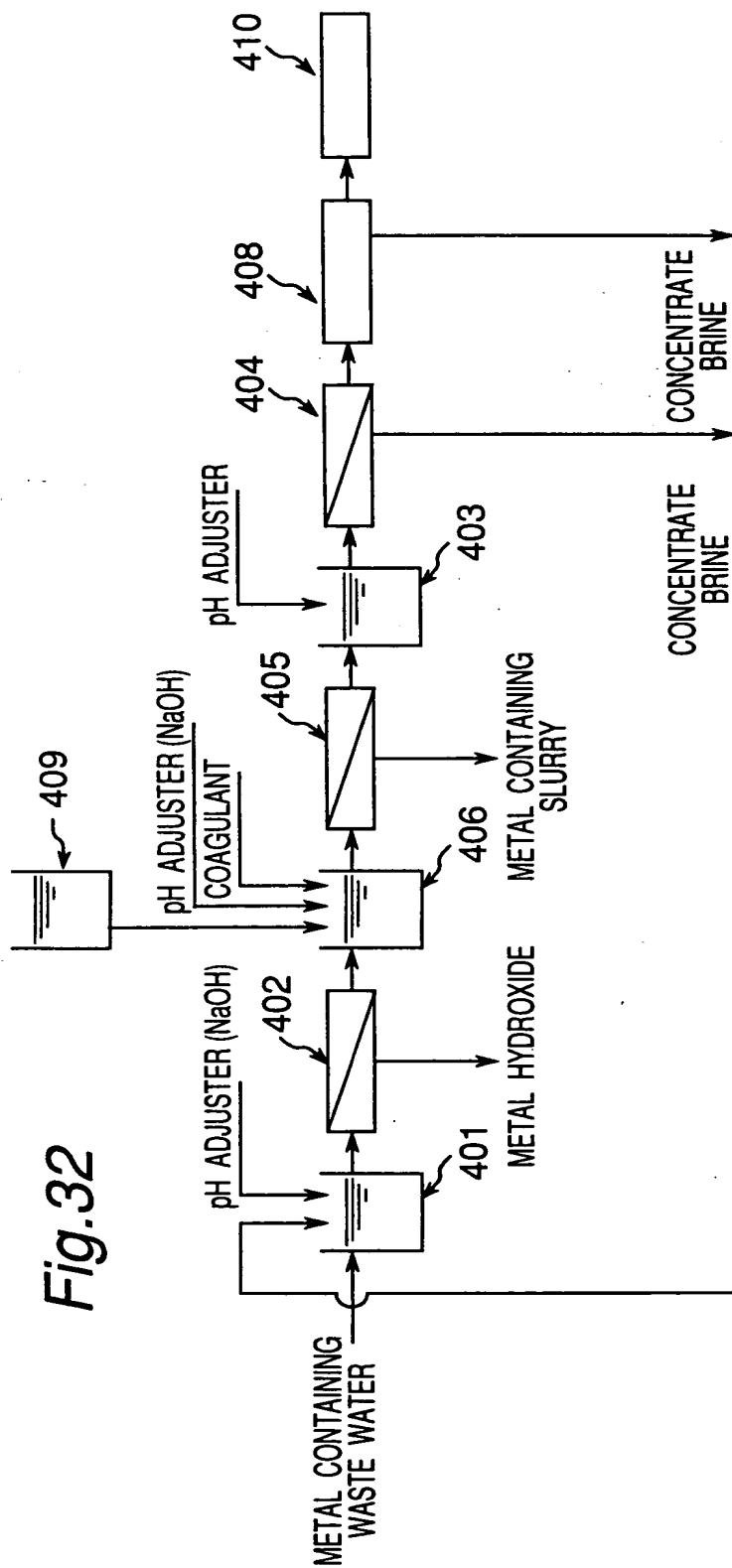


Fig.33

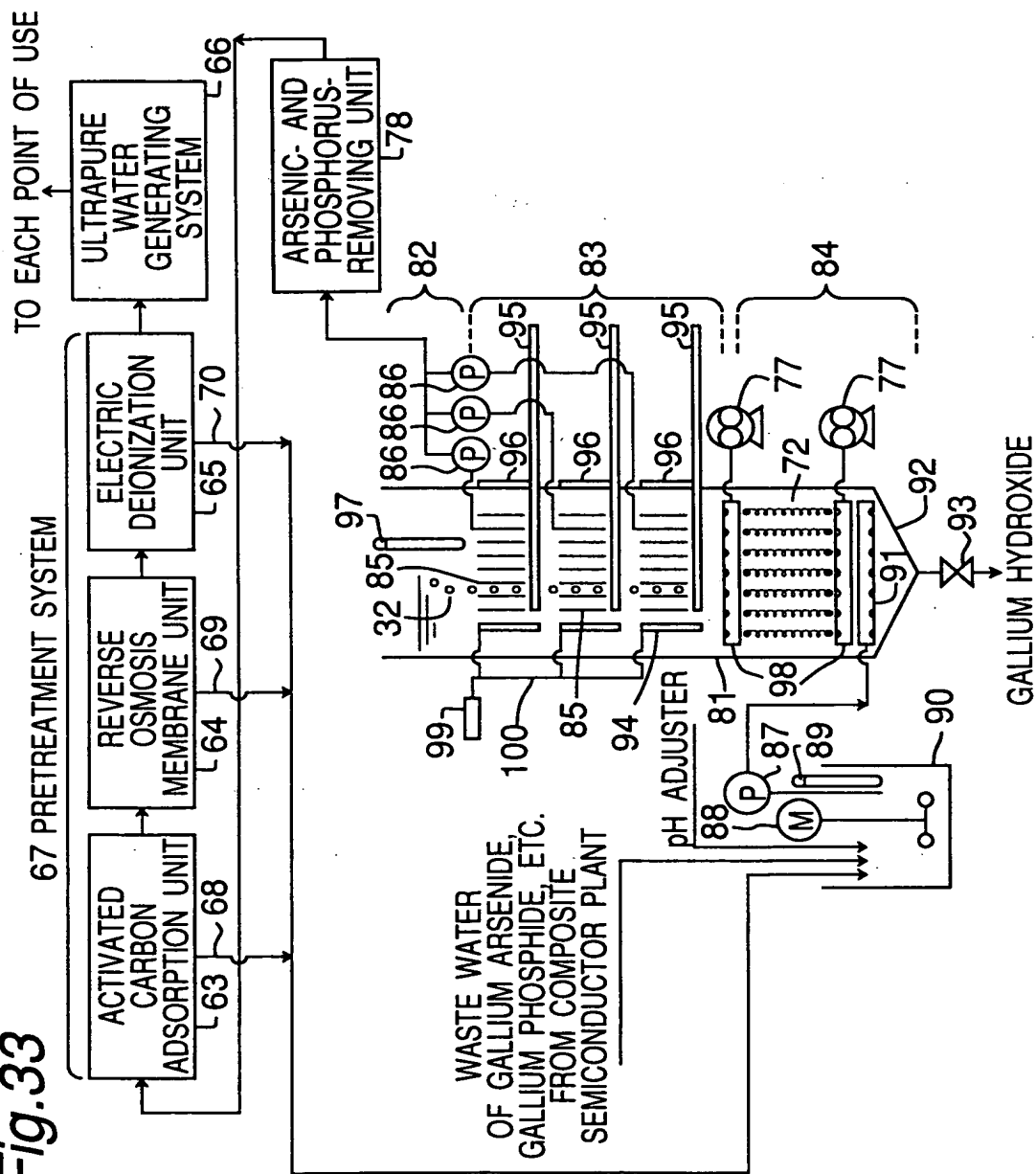


Fig.34

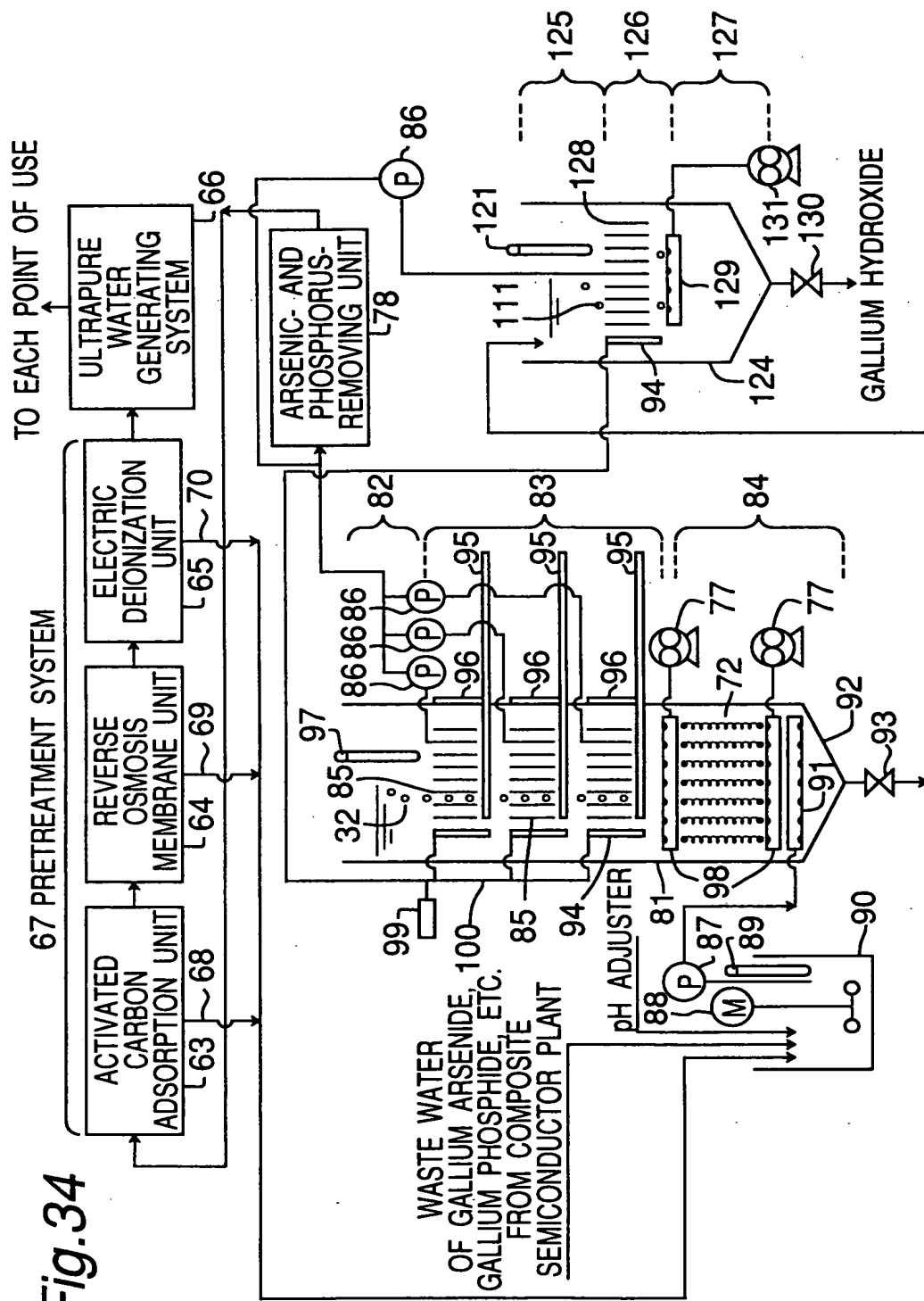
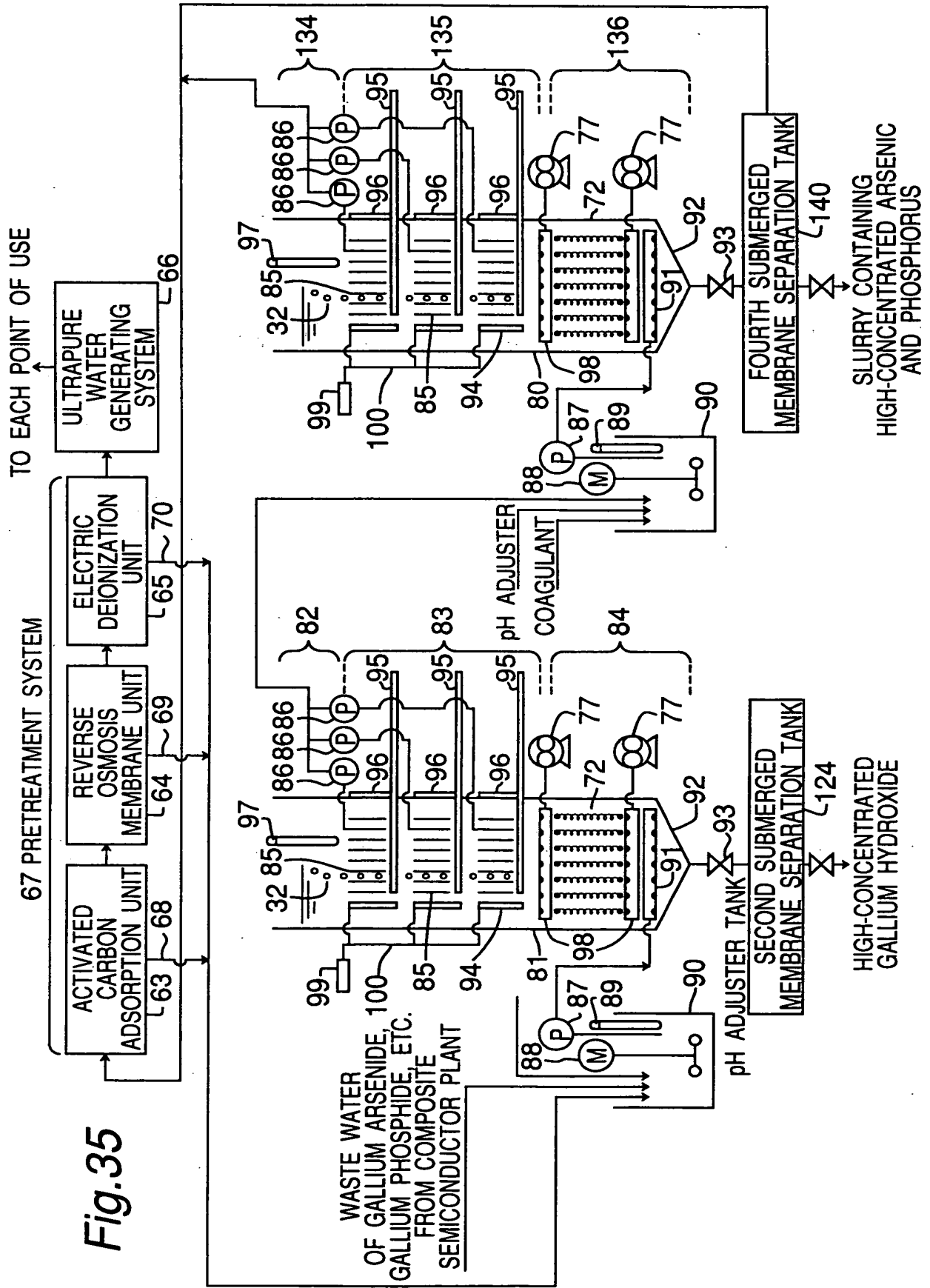


Fig.35



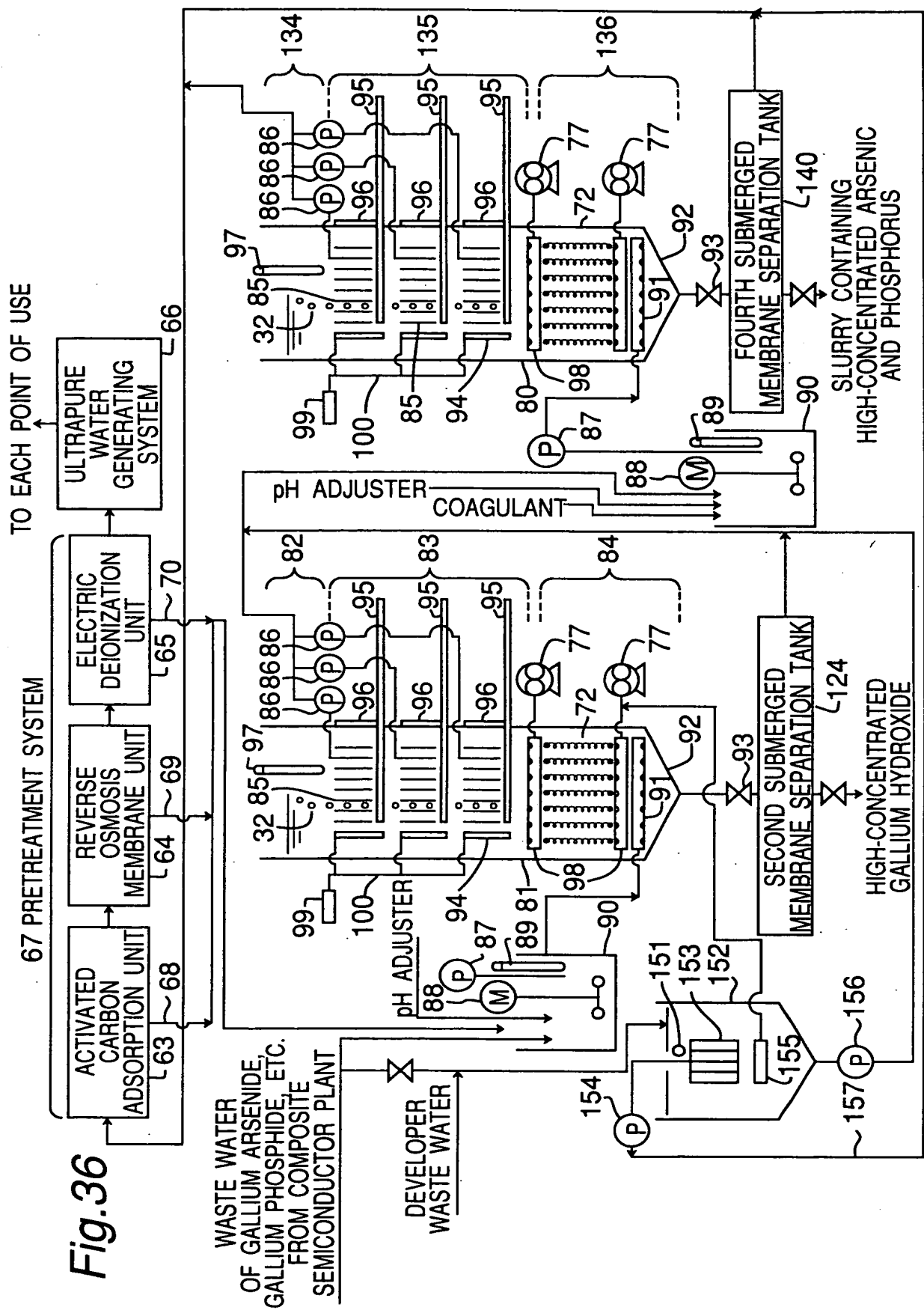


Fig.36

Fig.38

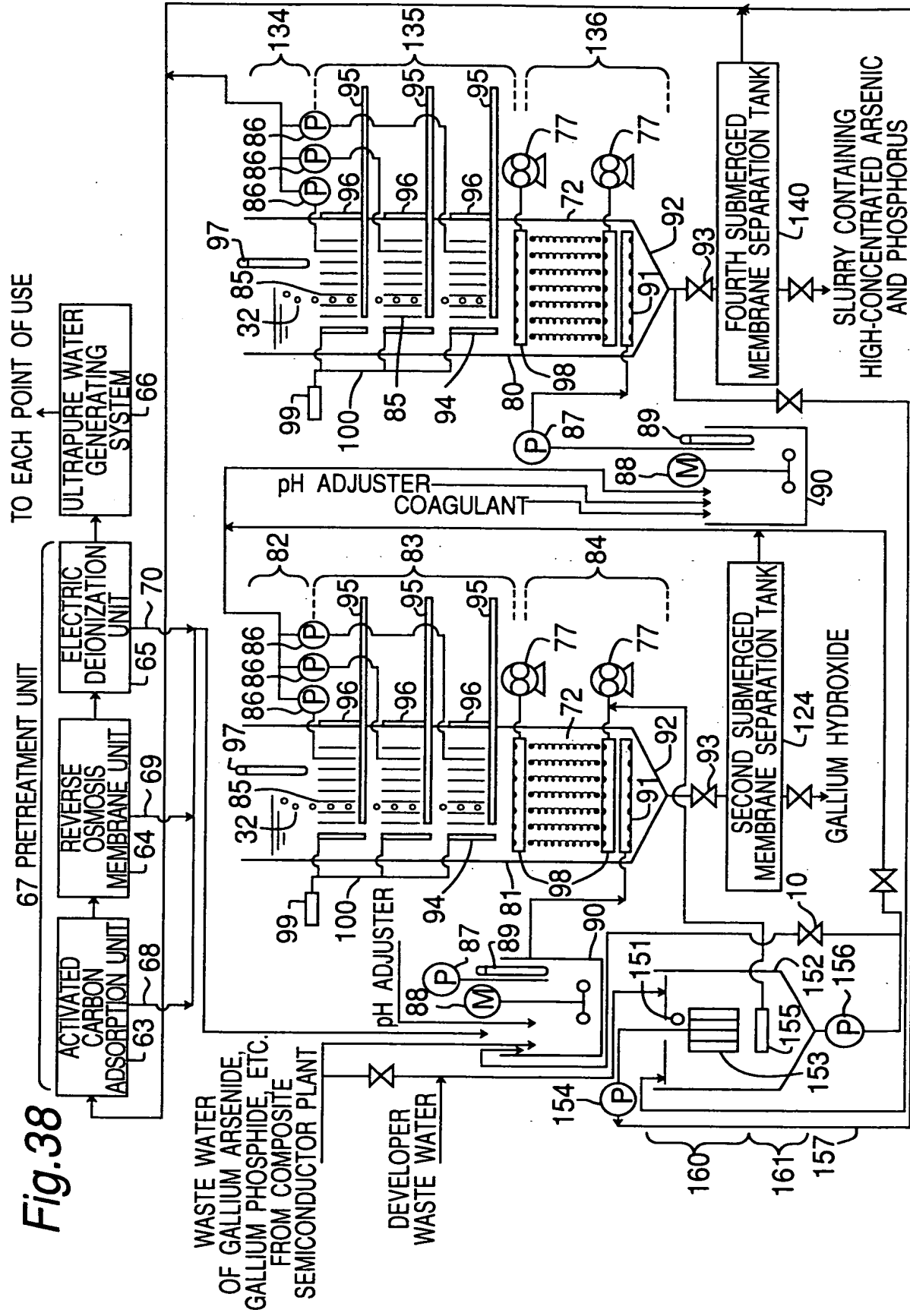


Fig.39

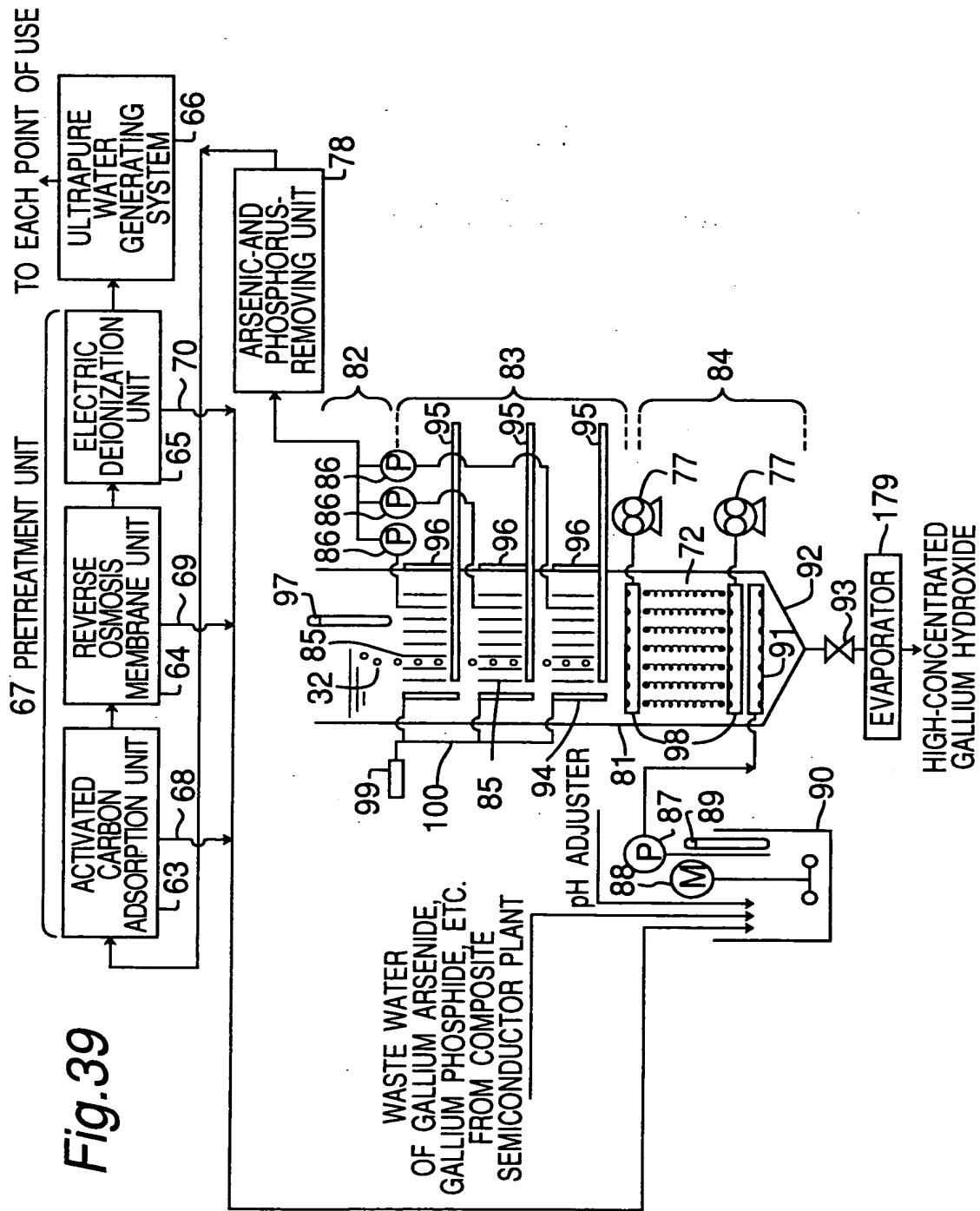


Fig. 40

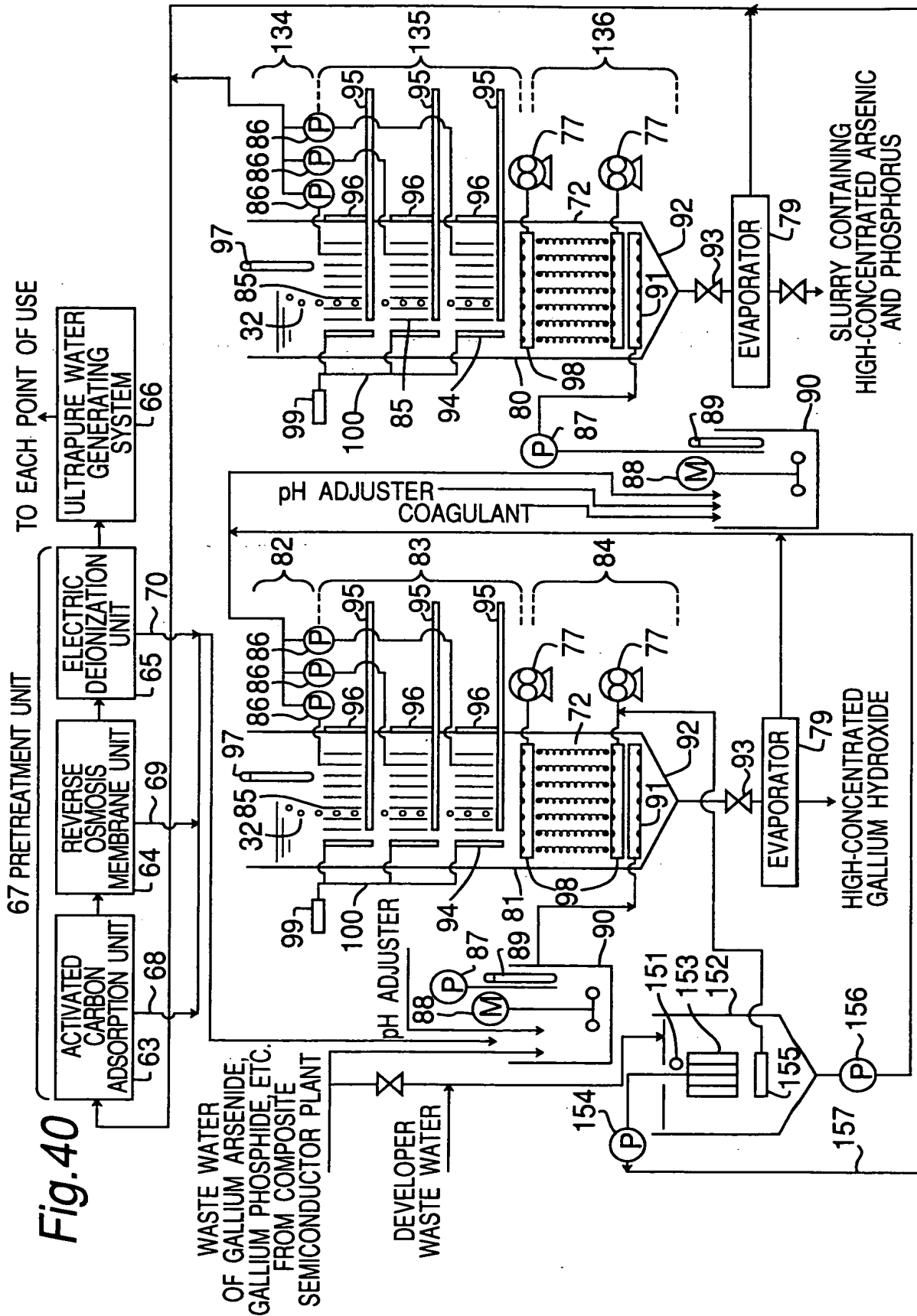


Fig. 41

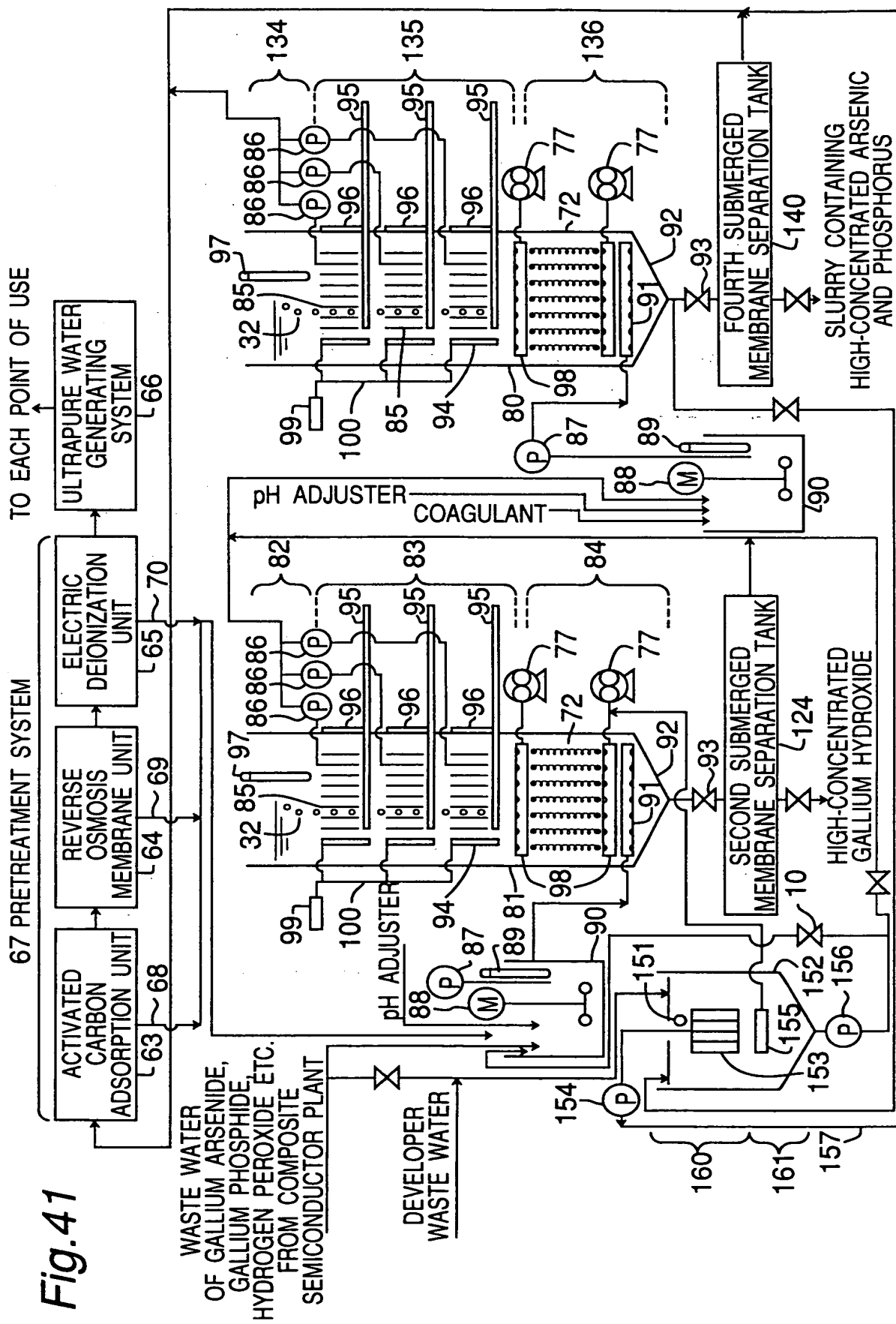


Fig.42A

WHEN CONCENTRATIONS OF GALLIUM AND ARSENIC ARE NORMAL CONCENTRATIONS

[illegible]

Fig.42B

WHEN CONCENTRATIONS OF GALLIUM AND ARSENIC ARE LOW CONCENTRATIONS

[illegible]

Fig. 43

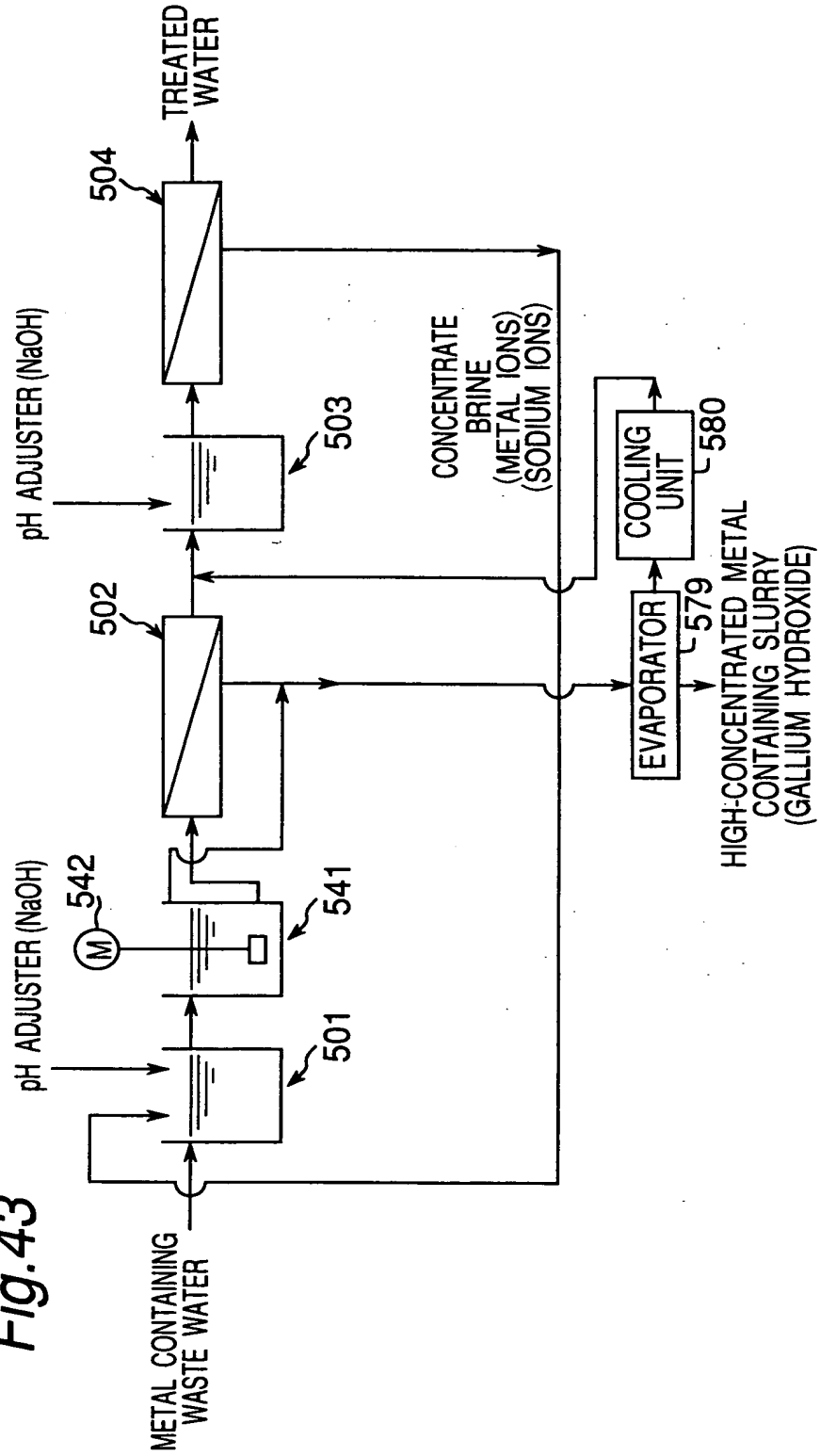


Fig. 44

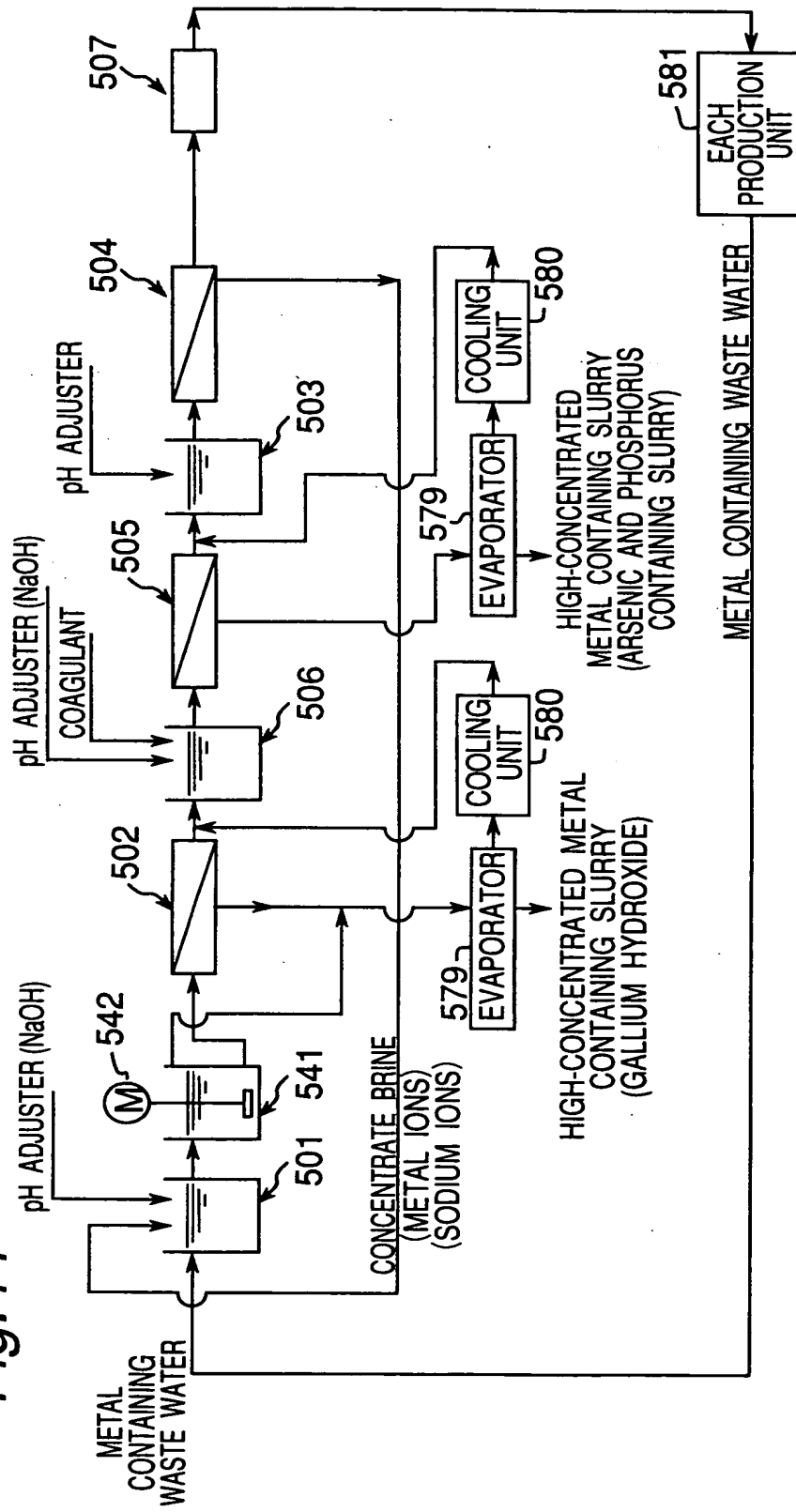


Fig.45

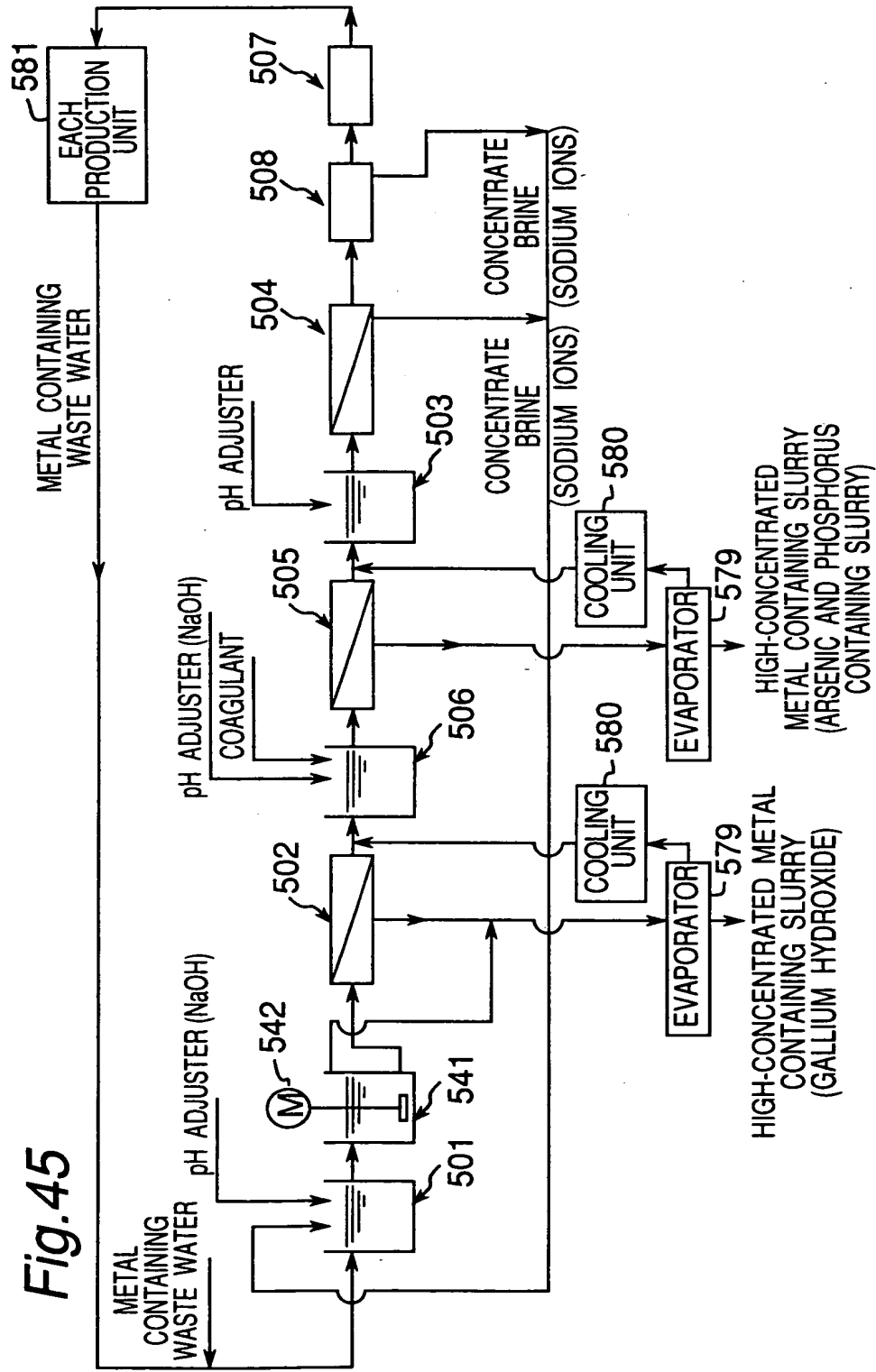


Fig.46

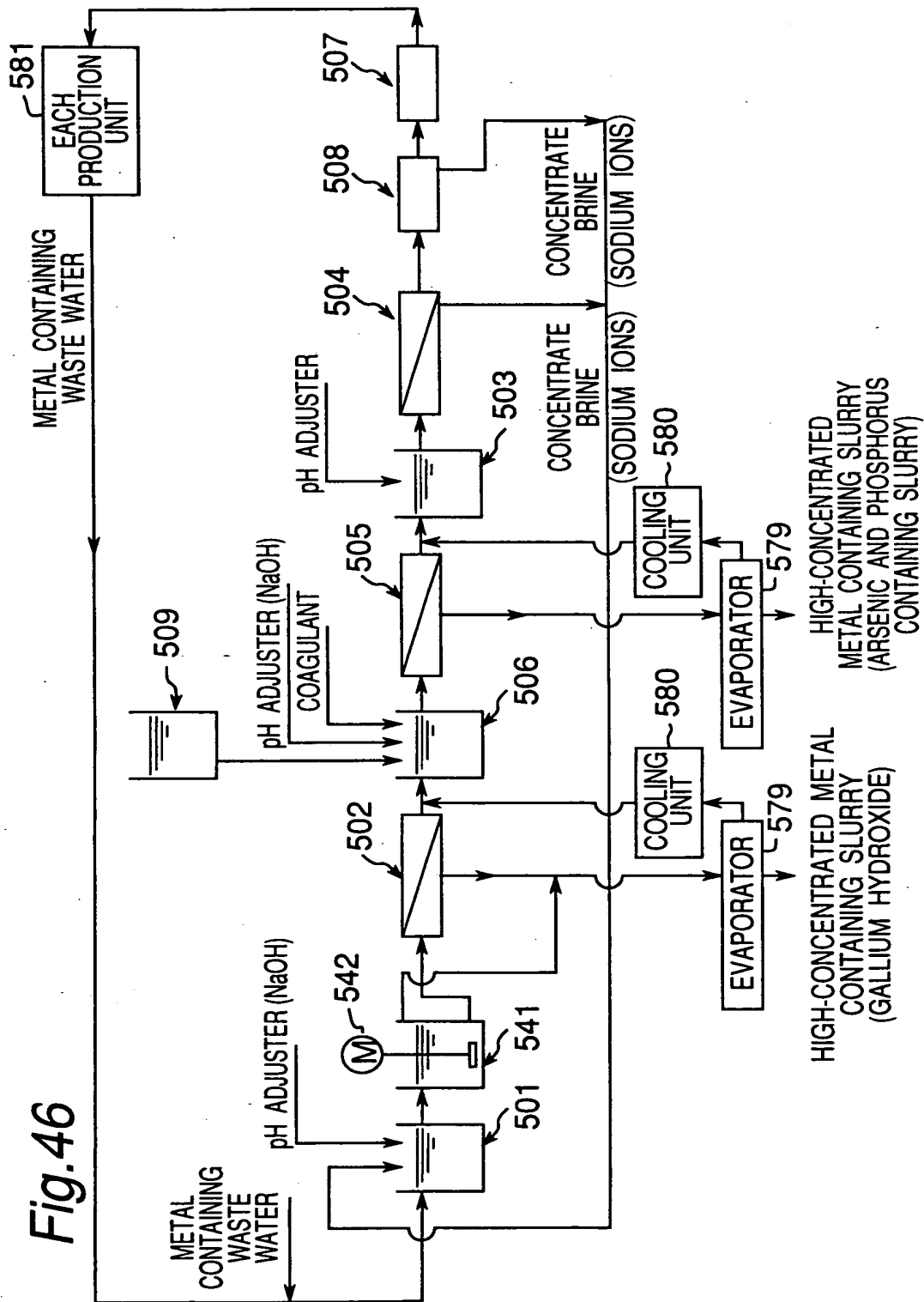


Fig.47

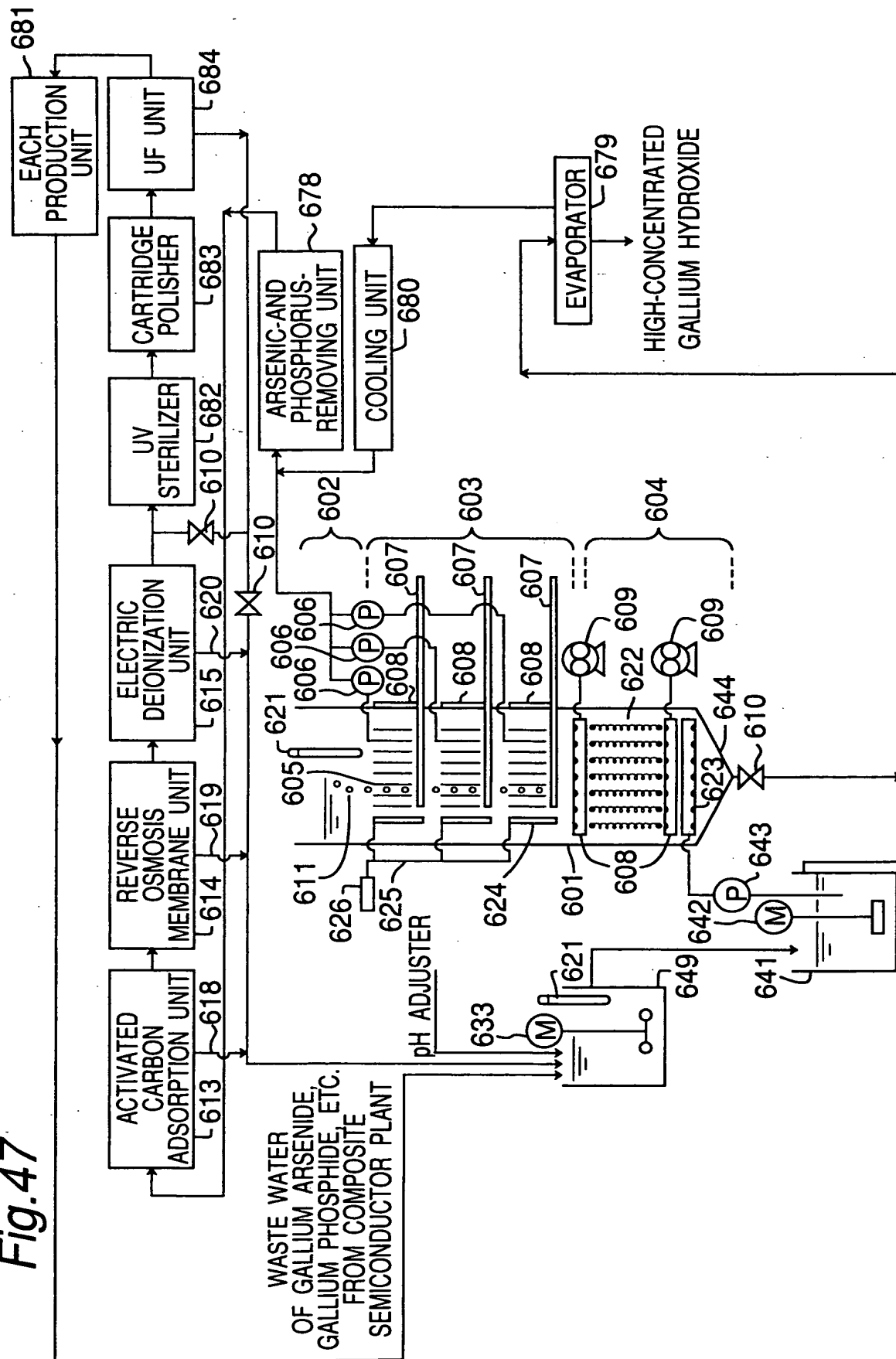


Fig. 48

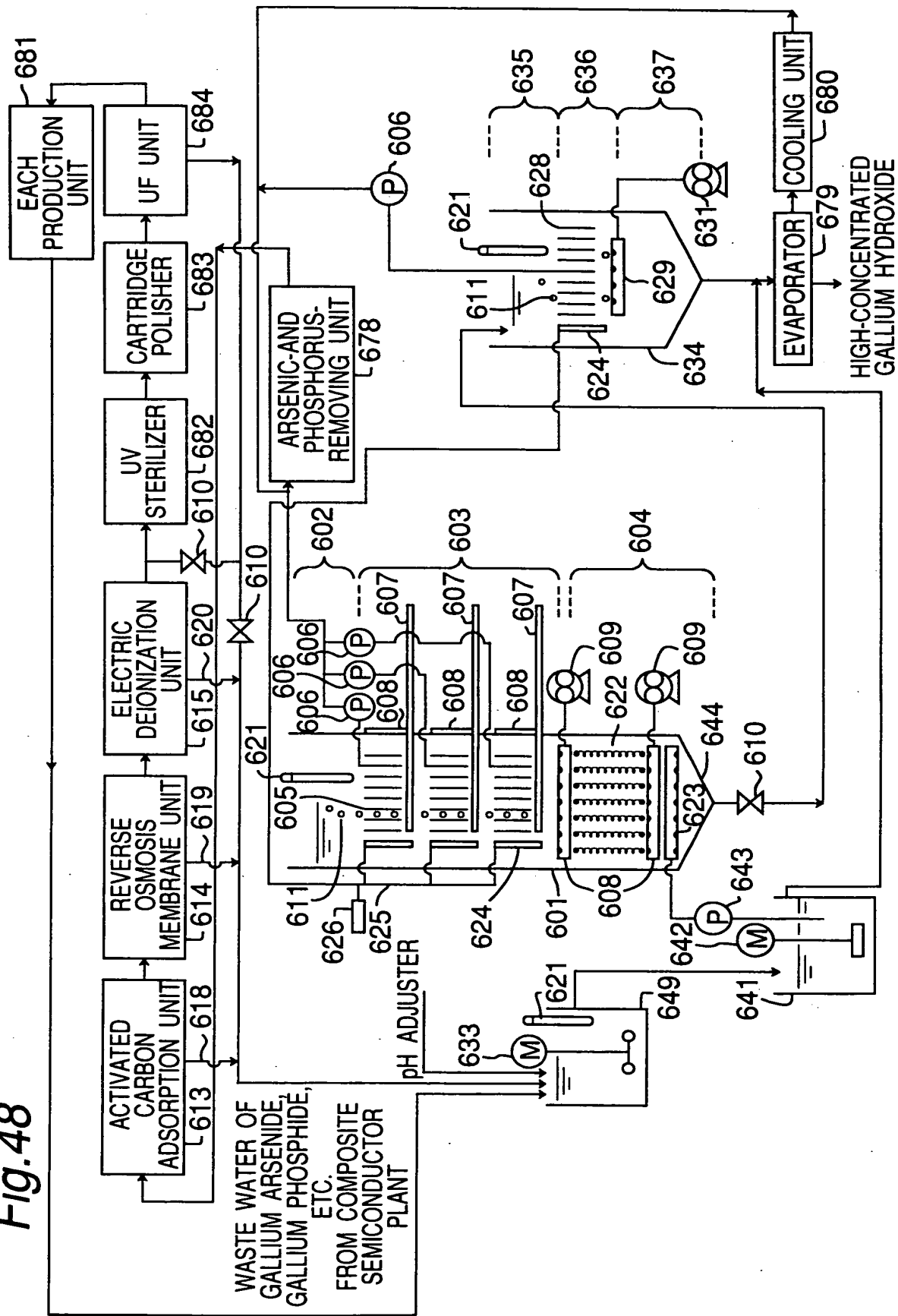


Fig.49

WASTE WATER OF GALLIUM ARSENIDE, GALLIUM PHOSPHIDE, ETC.
FROM COMPOSITE SEMICONDUCTOR PLANT

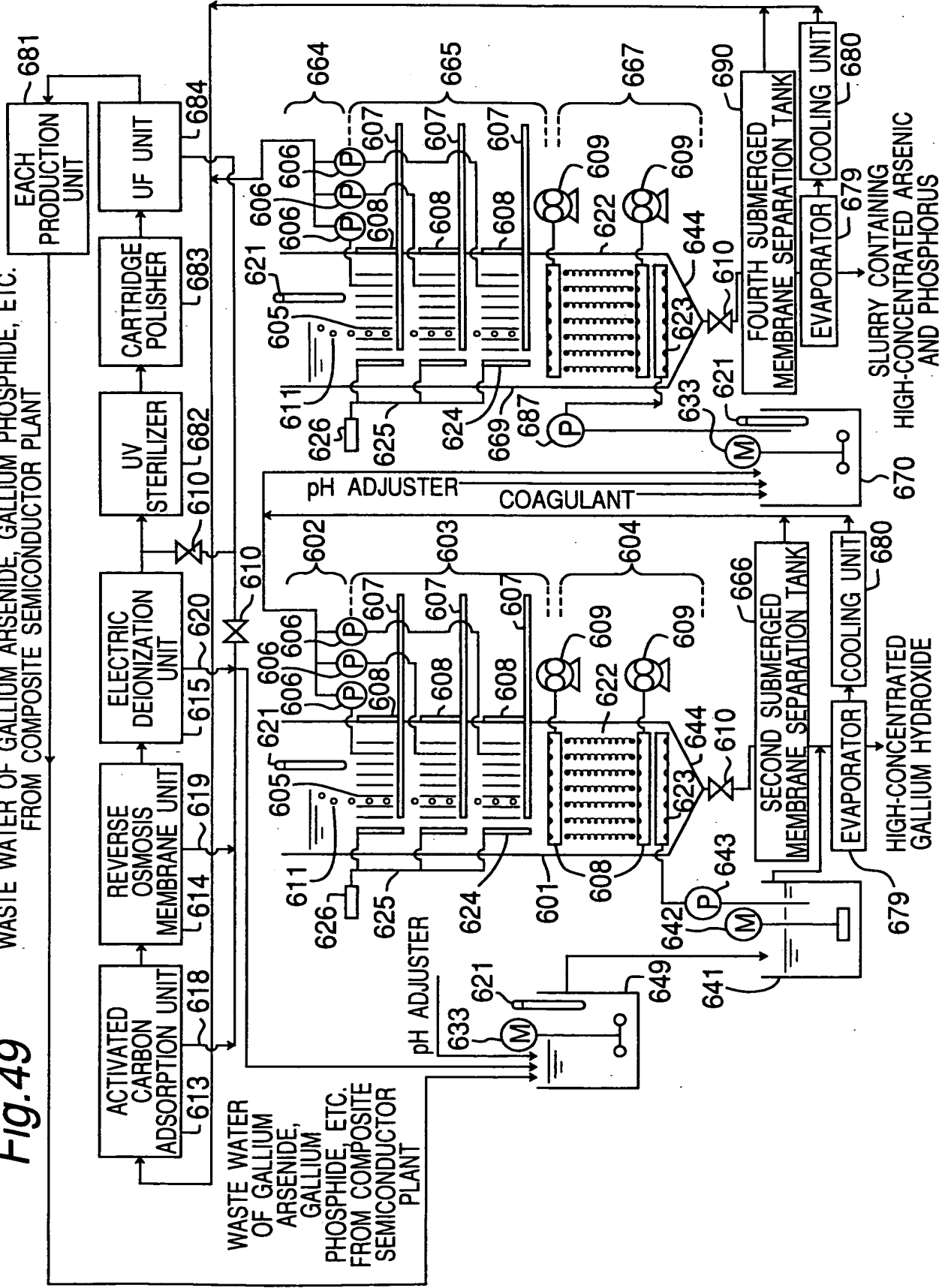


Fig.50

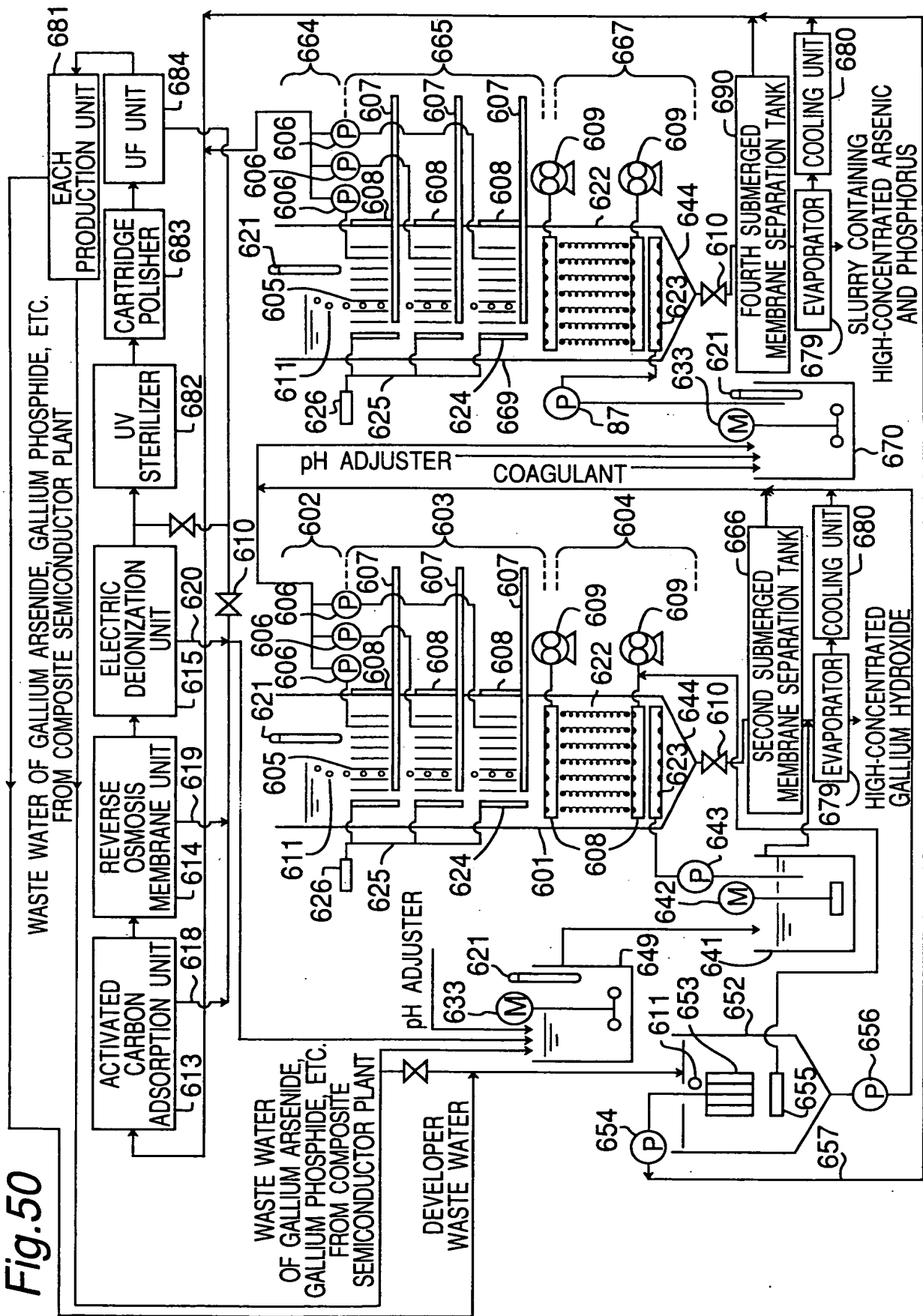


Fig.51

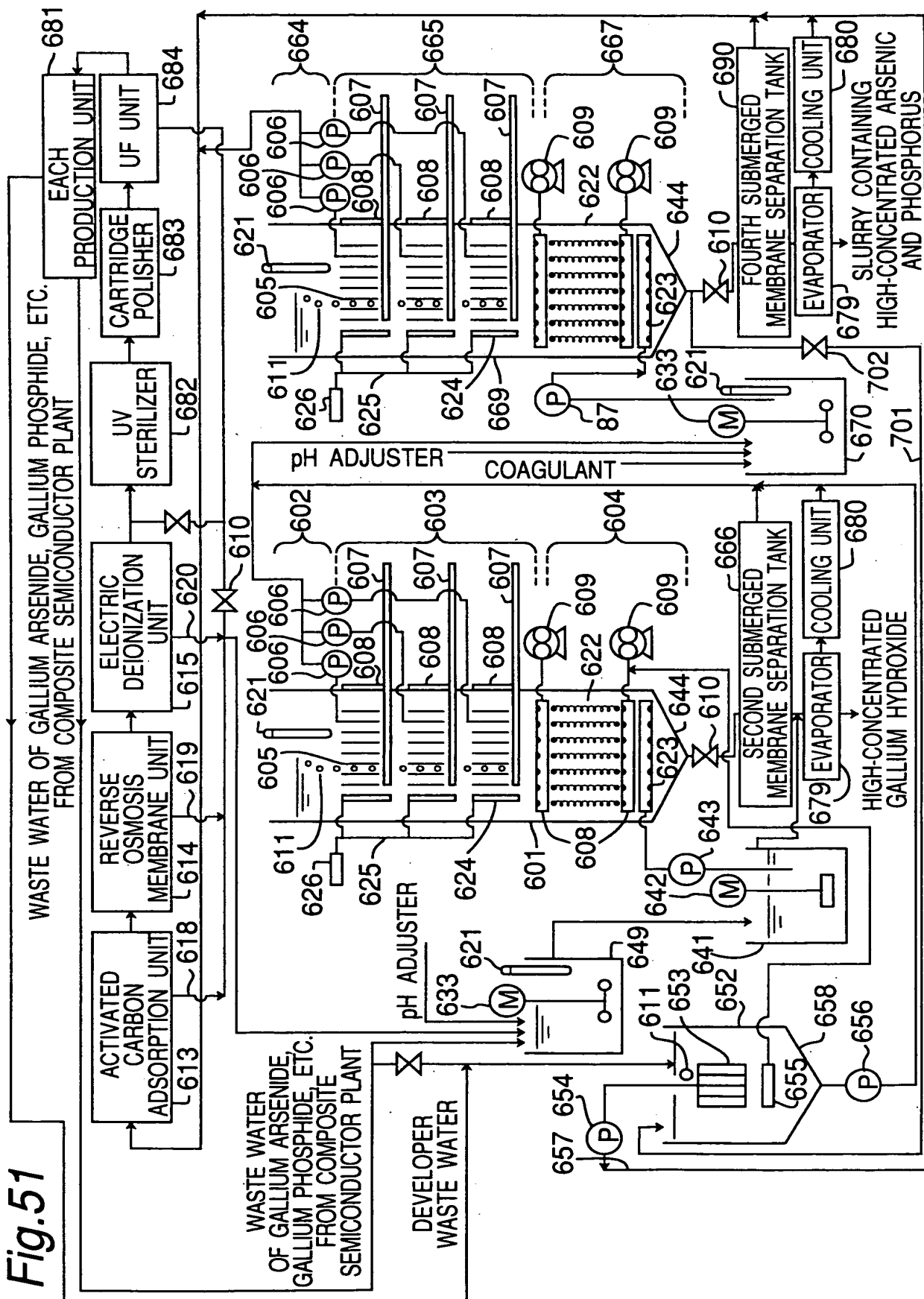


Fig.52

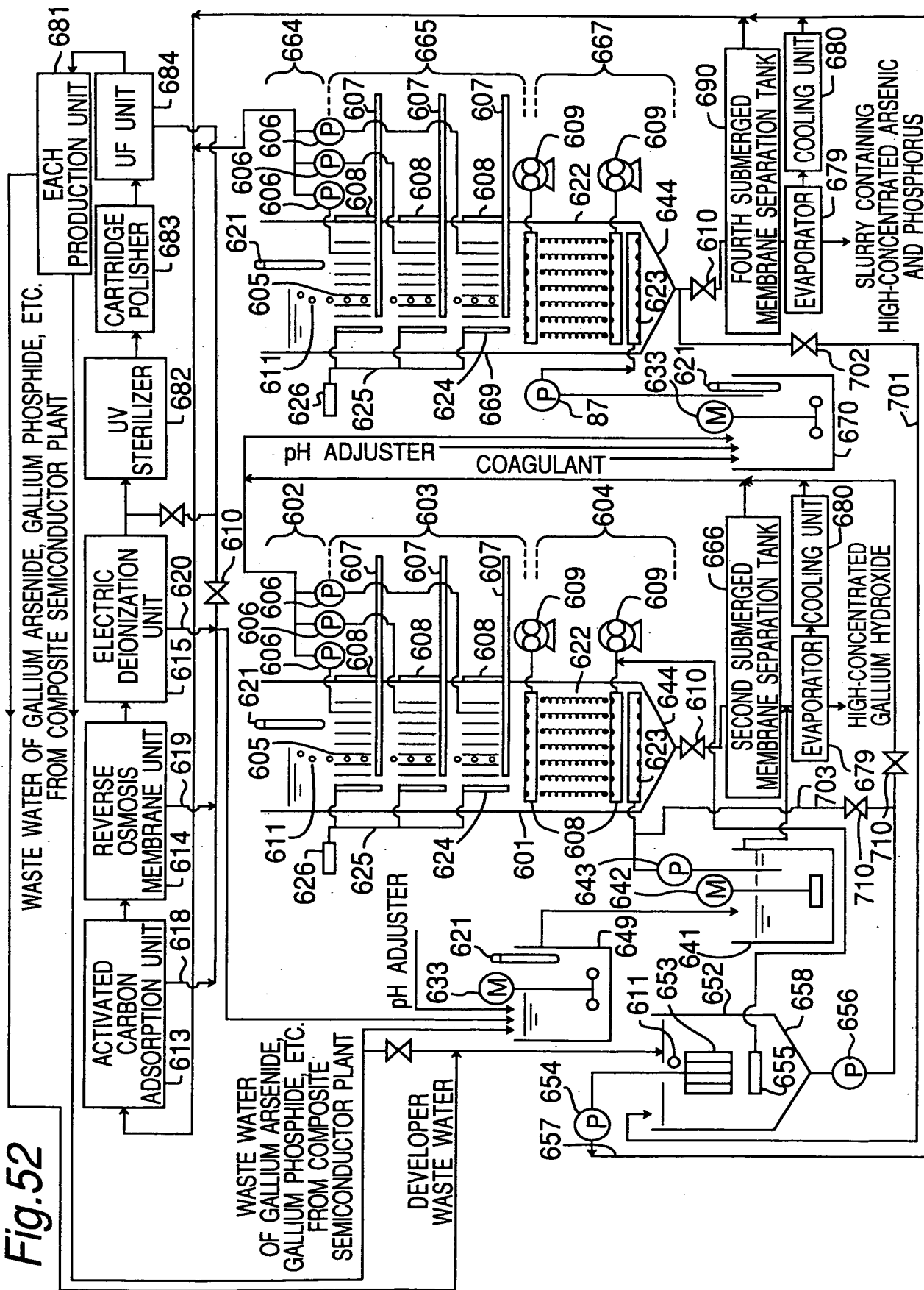


Fig.53

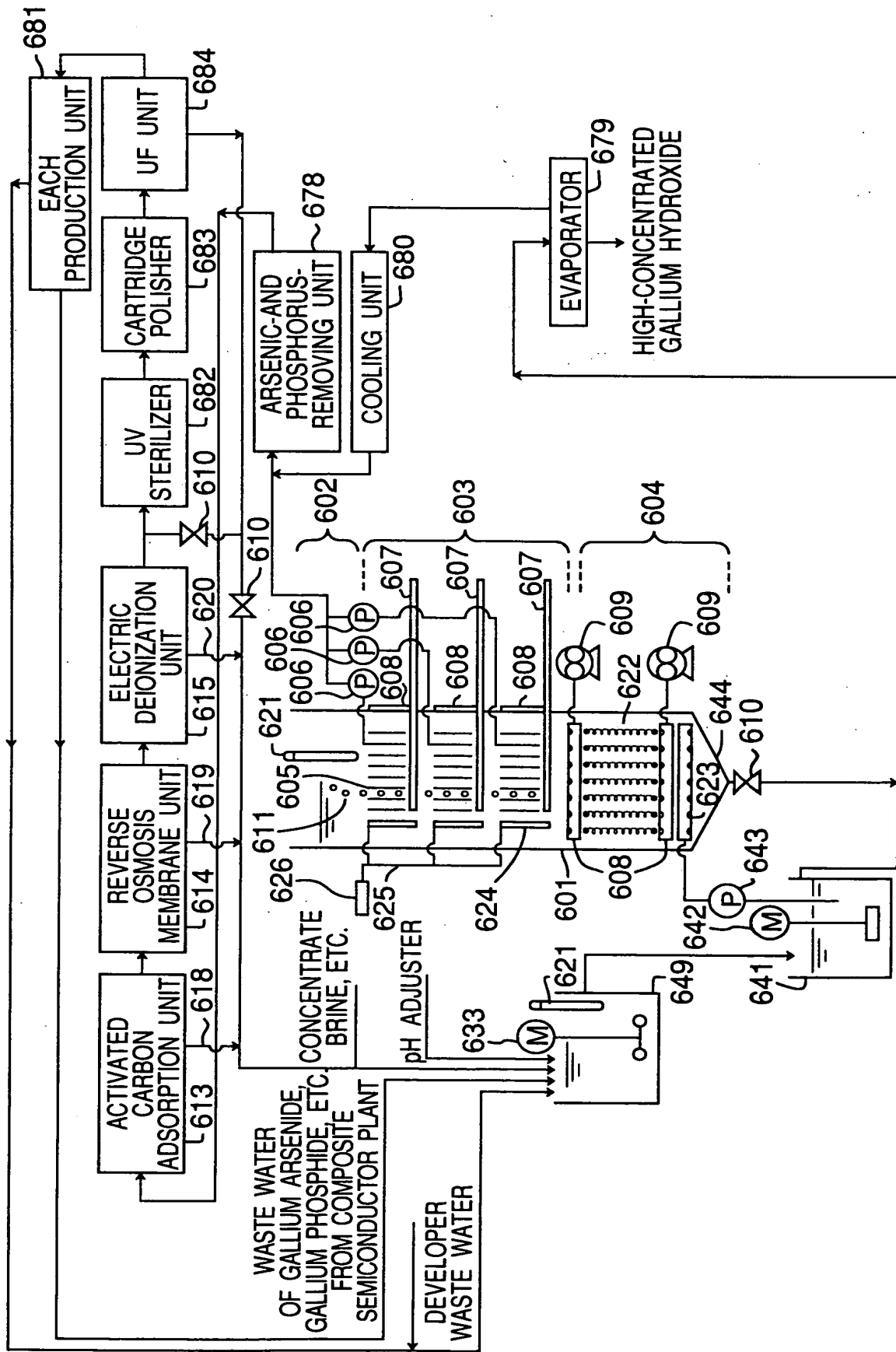


Fig. 54

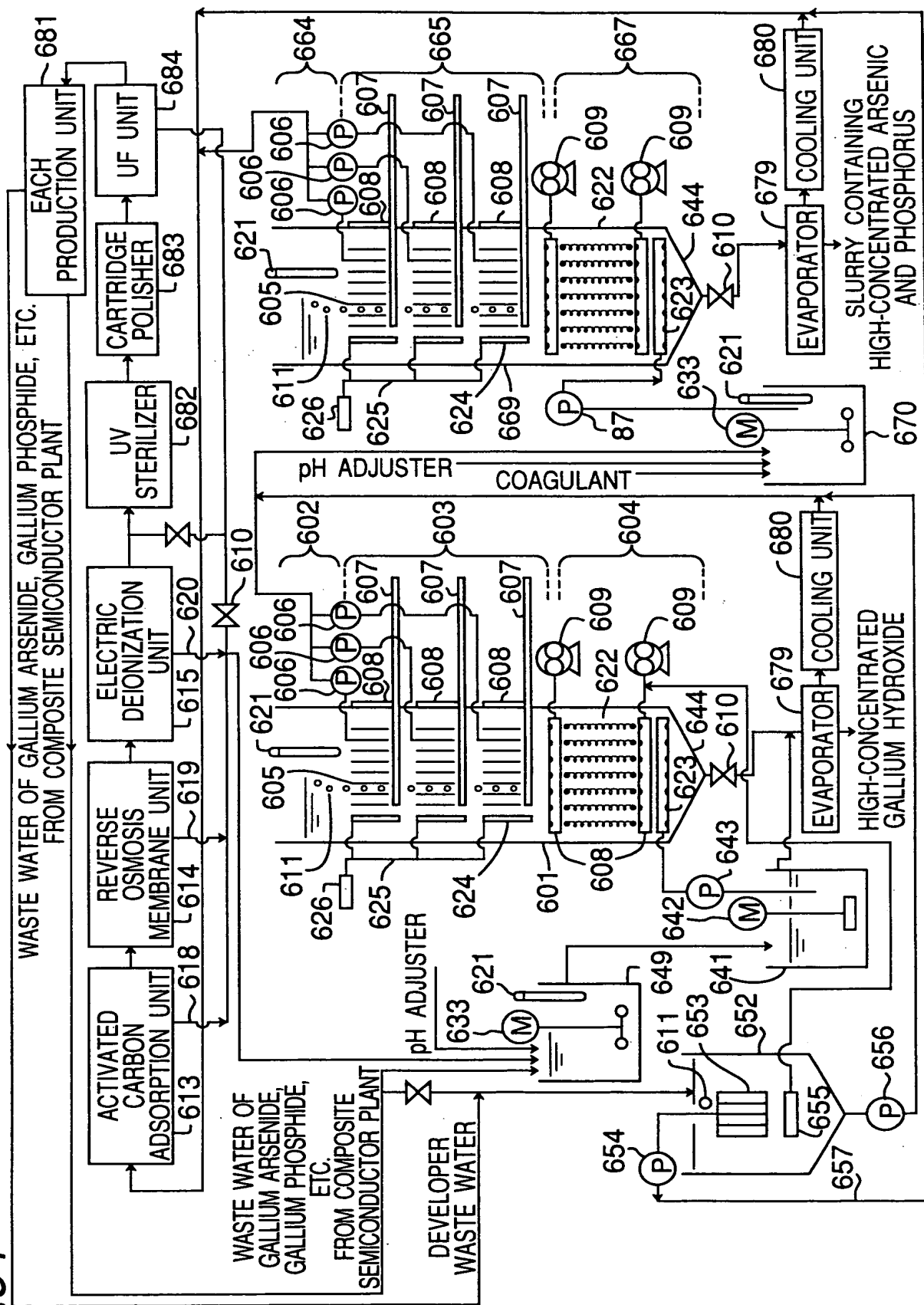


Fig.55

WASTE WATER OF GALLIUM ARSENIDE, GALLIUM PHOSPHIDE, HYDROGEN PEROXIDE ETC. FROM COMPOSITE SEMICONDUCTOR PLANT

WASTE WATER OF GALLIUM ARSENIDE, GALLIUM PHOSPHIDE, HYDROGEN PEROXIDE ETC. FROM COMPOSITE SEMICONDUCTOR PLANT

DEVELOPER WASTE WATER

ACTIVATED CARBON ADSORPTION UNIT

REVERSE OSMOSIS MEMBRANE UNIT

ELECTRIC DEIONIZATION UNIT

UV STERILIZER

CARTRIDGE POLISHER

UF UNIT

PRODUCTION UNIT

PH ADJUSTER

COAGULANT

SECOND SUBMERGED MEMBRANE SEPARATION TANK

FOURTH SUBMERGED MEMBRANE SEPARATION TANK

EVAPORATOR

COOLING UNIT

HIGH-CONCENTRATED GALLIUM HYDROXIDE

SLURRY CONTAINING HIGH-CONCENTRATED ARSENIC AND PHOSPHORUS

Fig.55

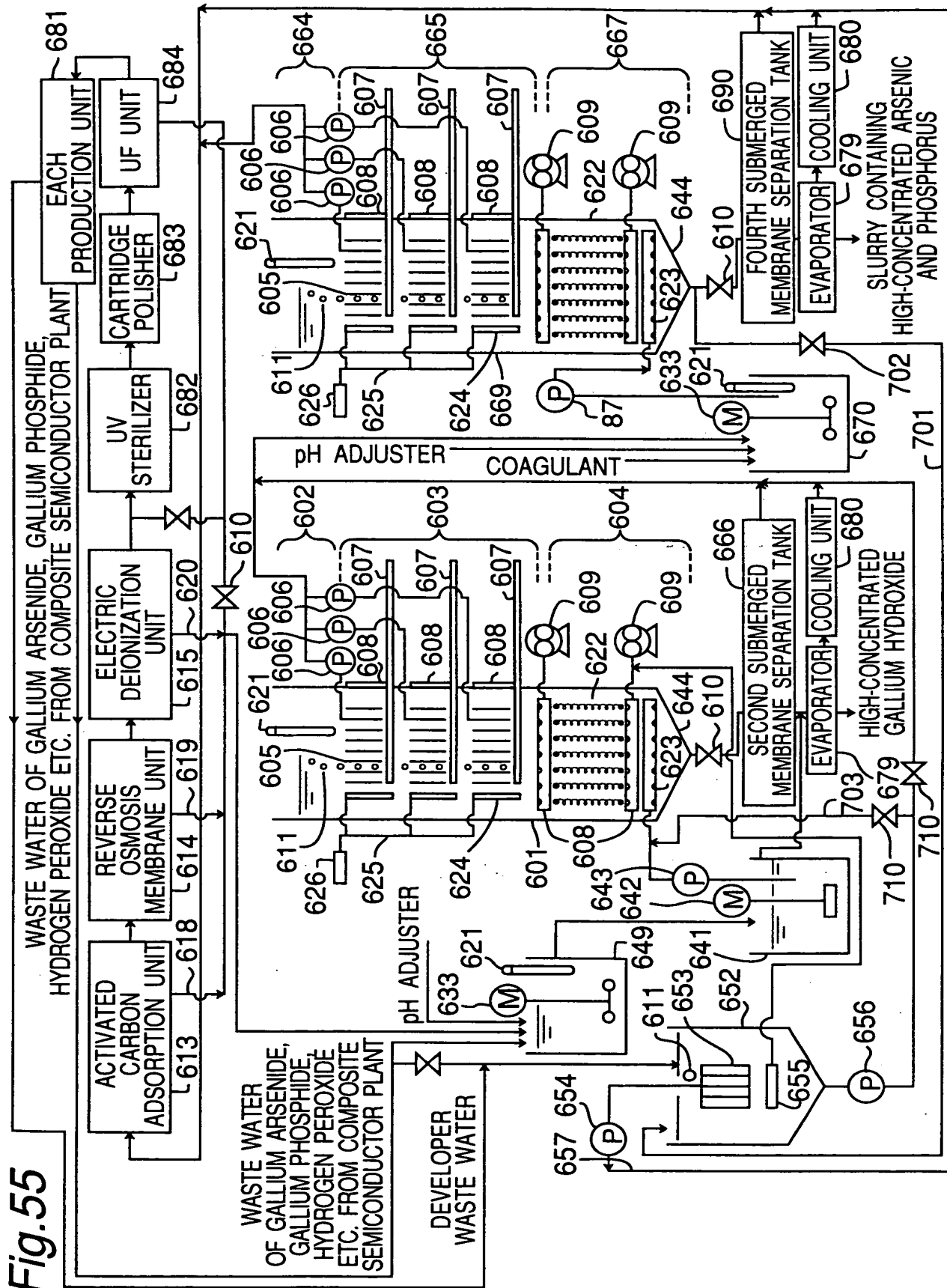


Fig.56A

WHEN CONCENTRATIONS OF GALLIUM AND ARSENIC ARE NORMAL CONCENTRATIONS

[illegible]

Fig.56B

WHEN CONCENTRATIONS OF GALLIUM AND ARSENIC ARE LOW CONCENTRATIONS

[illegible]

Fig.57

STRUCTURE OF FOAM SEPARATION TANK

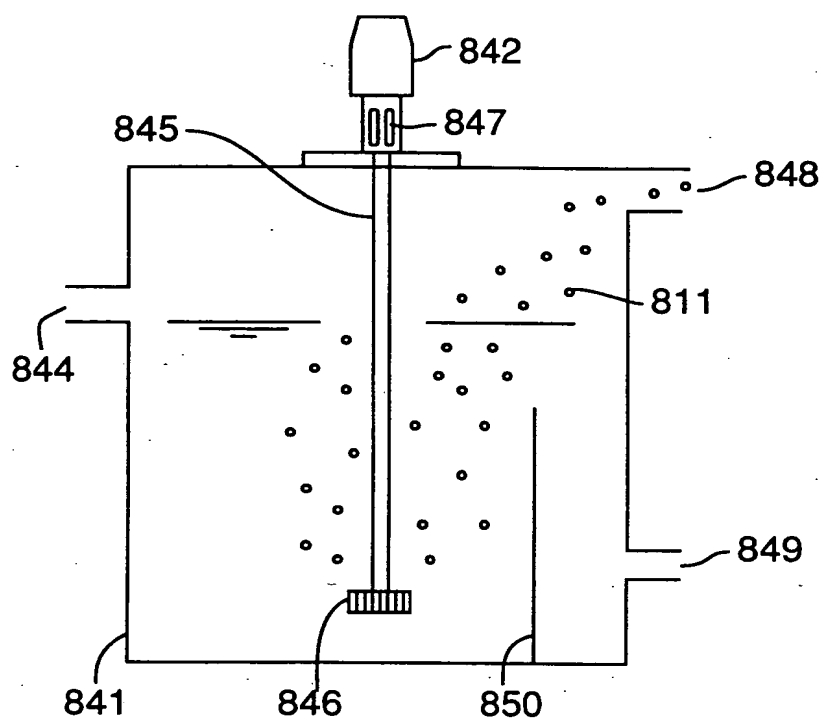


Fig. 58

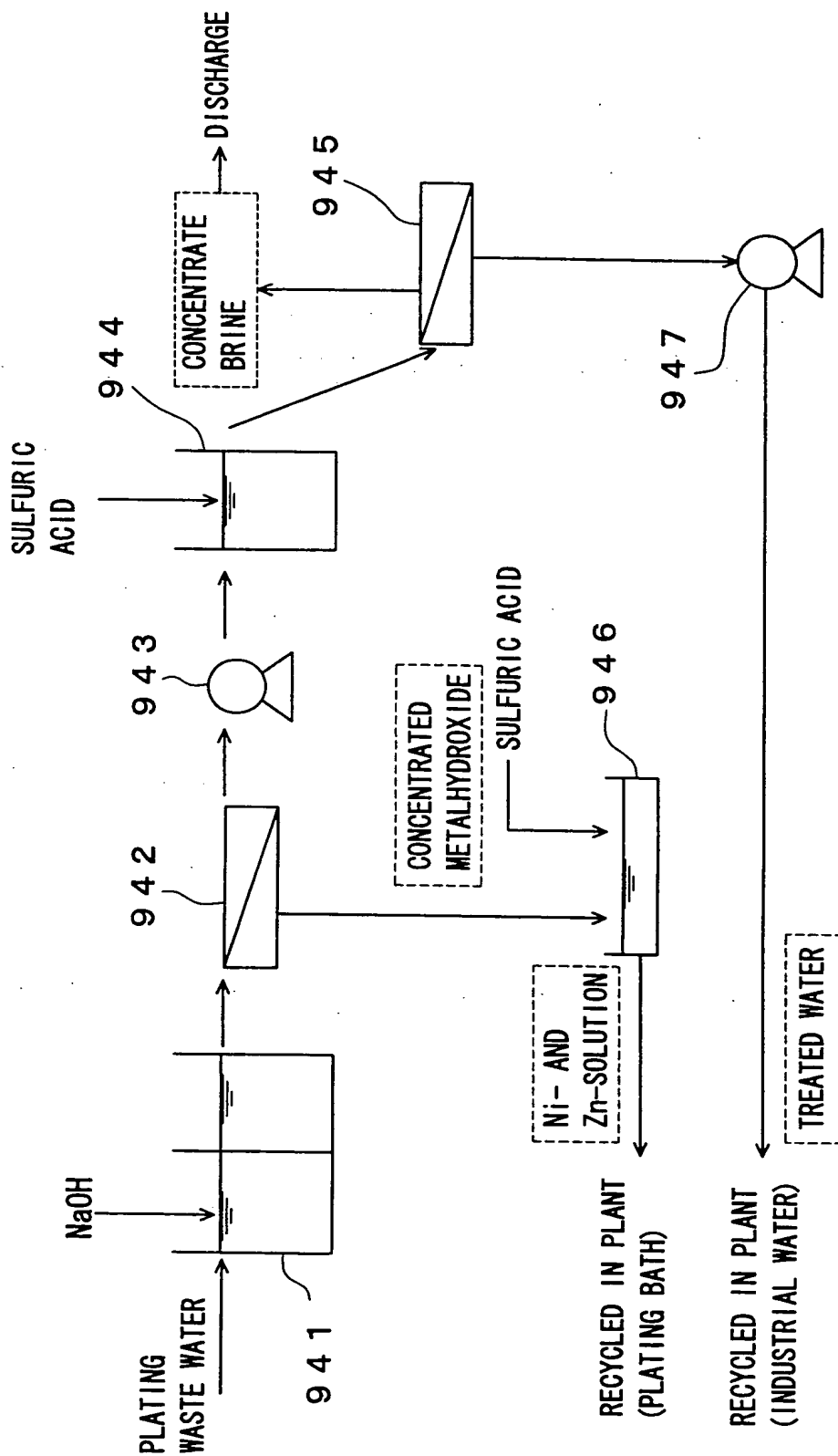


Fig. 59

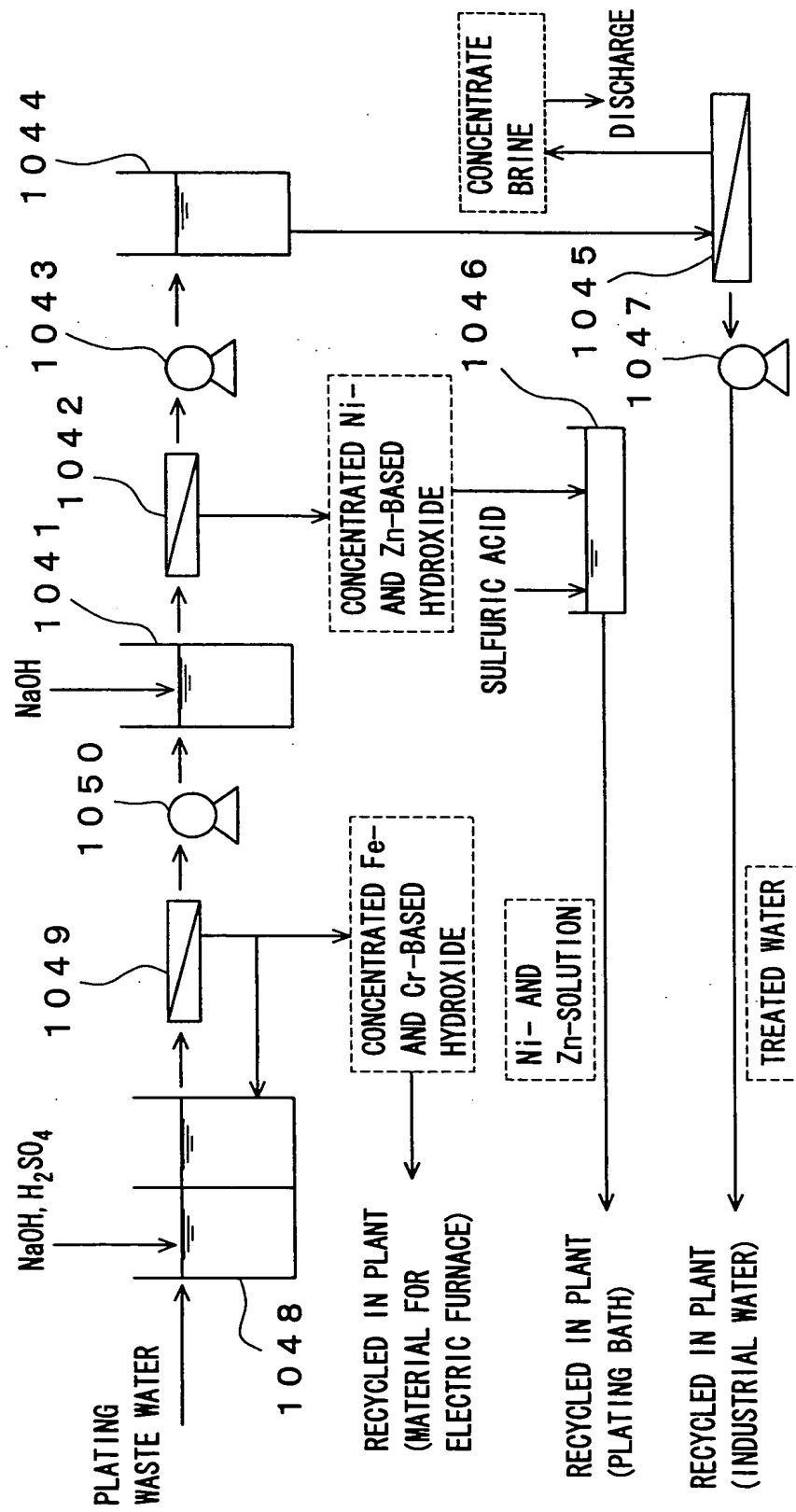


Fig. 60

